

ALS User's Meeting, Berkeley, CA
October 2000

Ultrafast X-ray Diffraction in Solids using K Radiation from Femtosecond Laser Generated Plasma Sources

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J.A. Squier, C.P.J. Barty, K.R. Wilson
University of California, San Diego, U.S.A.***

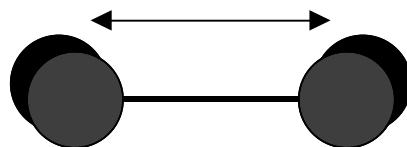
***K. Sokolowski-Tinten and D. von der Linde
Universität Essen, Germany***

Why ultrafast x-rays ?



Directly observe ultrafast atomic motion

1 Å or ~10 keV



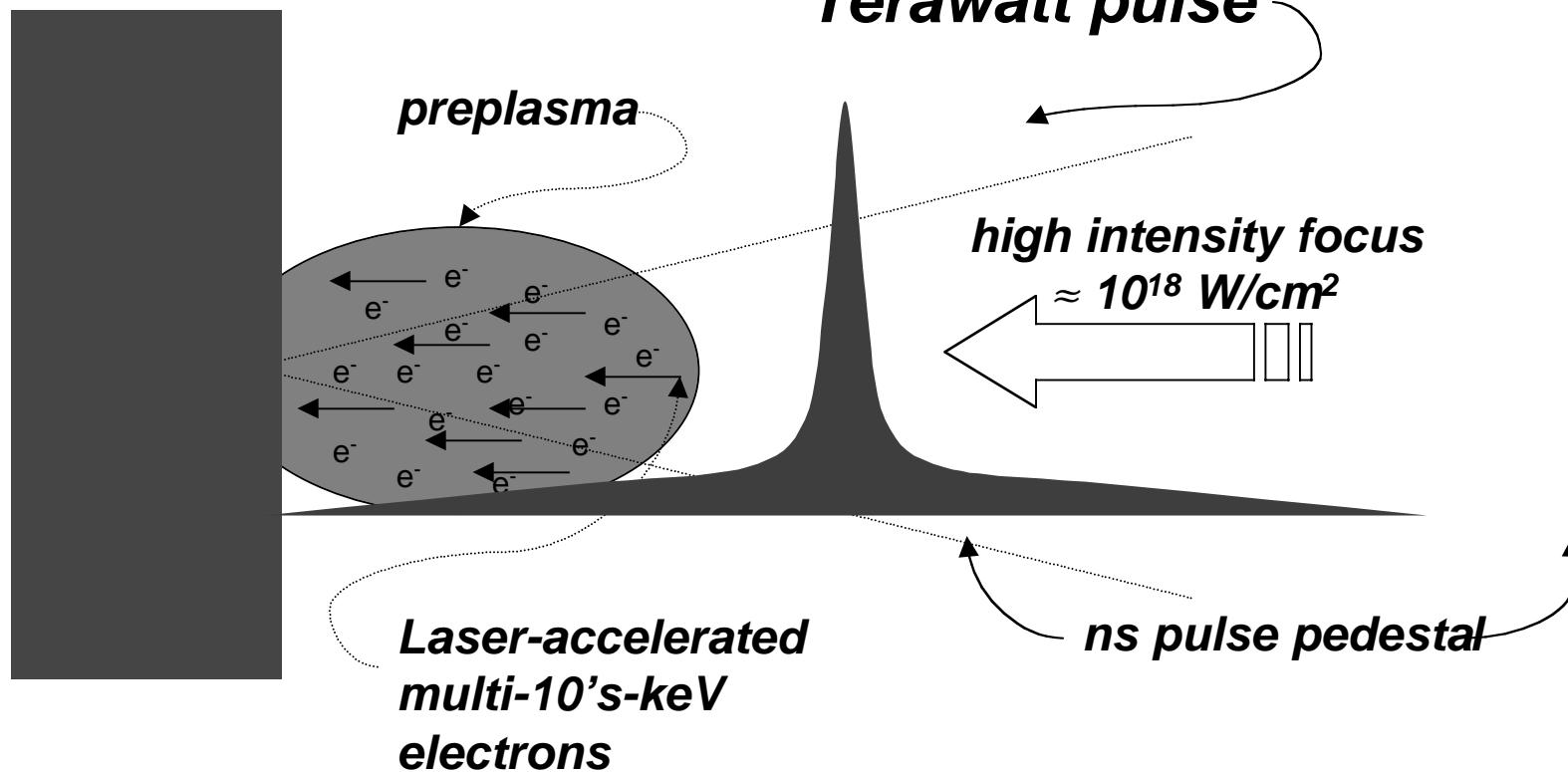
1) Short pulses (fs to ps)

2) Hard x-ray radiation

Laser-driven Electrons for Fast X-rays



solid target

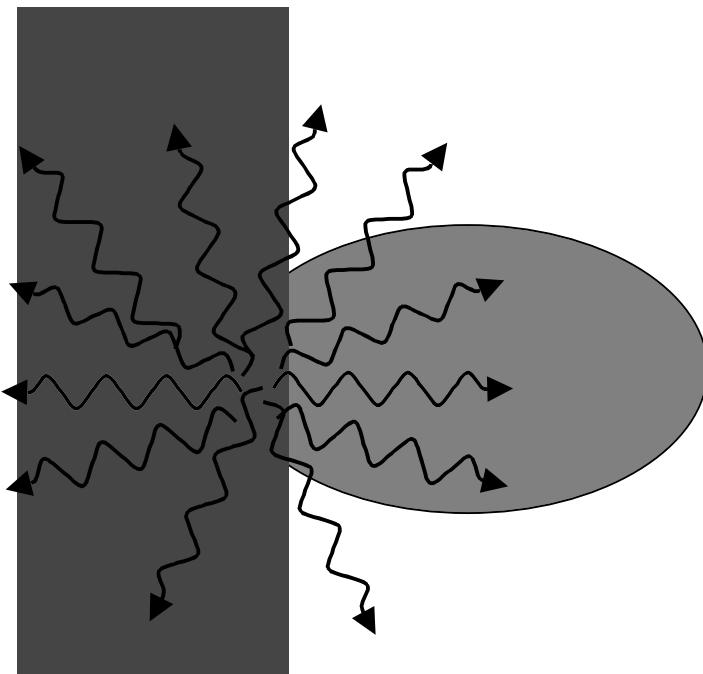


J.D. Kmetec, et al., *Phys. Rev. Lett.* **68**, 1527 (1990).

Laser-driven Electrons for Fast X-rays



solid target

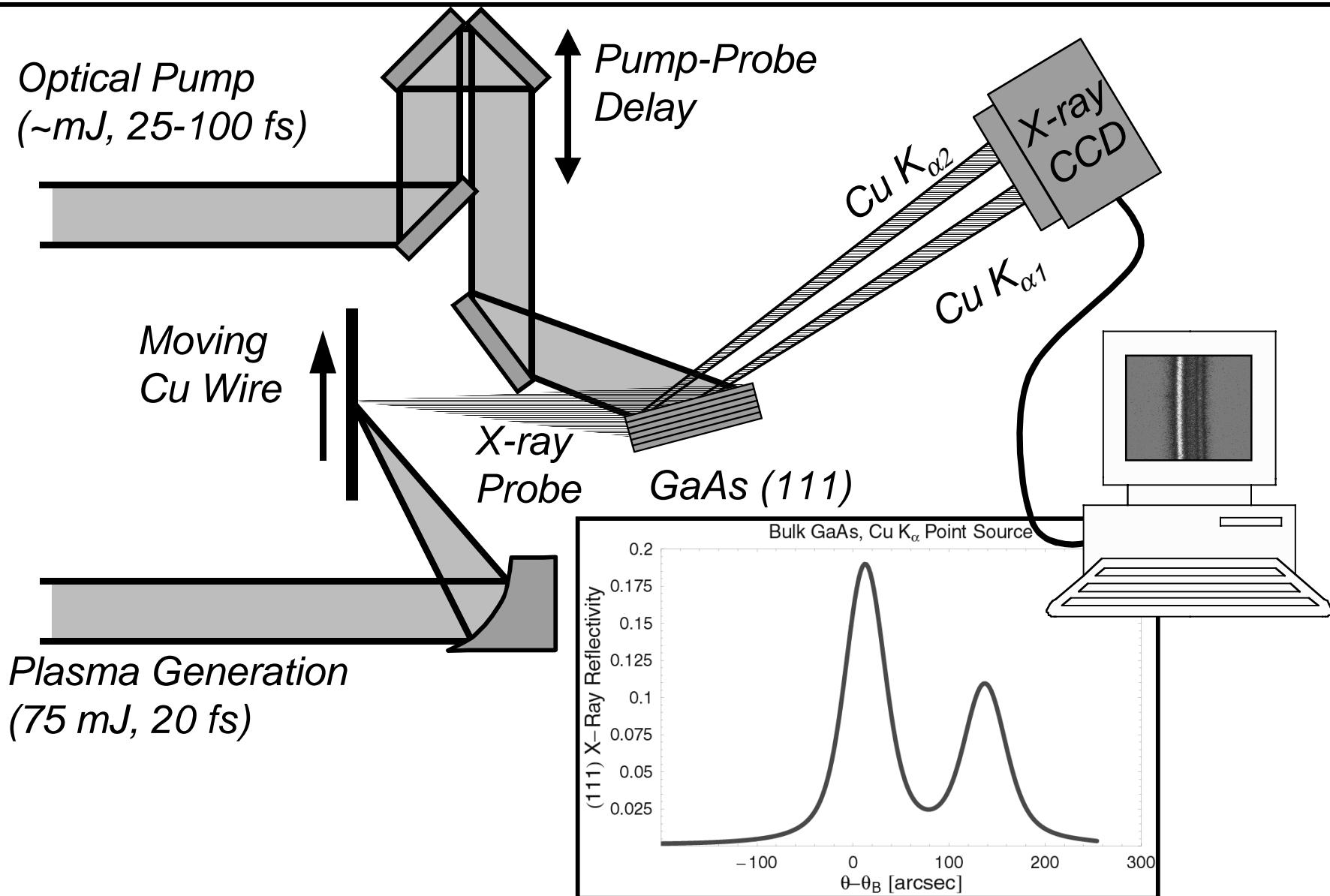


- **x-ray pulse duration:**
 $\Delta t_{\text{electron}}$ and stopping time
- ~ 200 fs at ENSTA
- Source size ~ laser spot
- 10^9 photons / shot

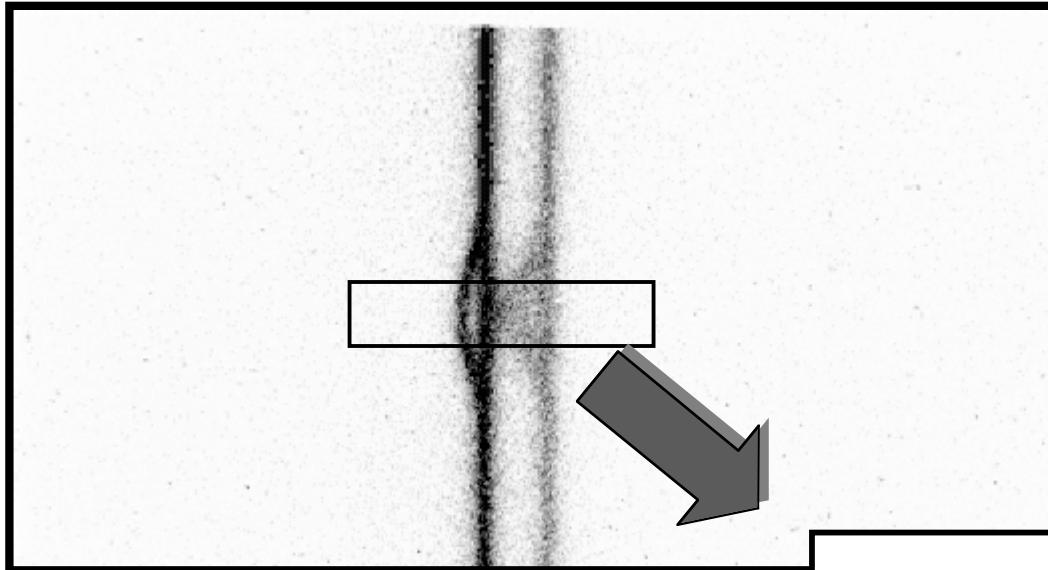
Bremsstrahlung and K_α radiation

J.D. Kmetec, et al., *Phys. Rev. Lett.* **68**, 1527 (1990).

Ultrafast X-ray Diffraction



Vertical Position



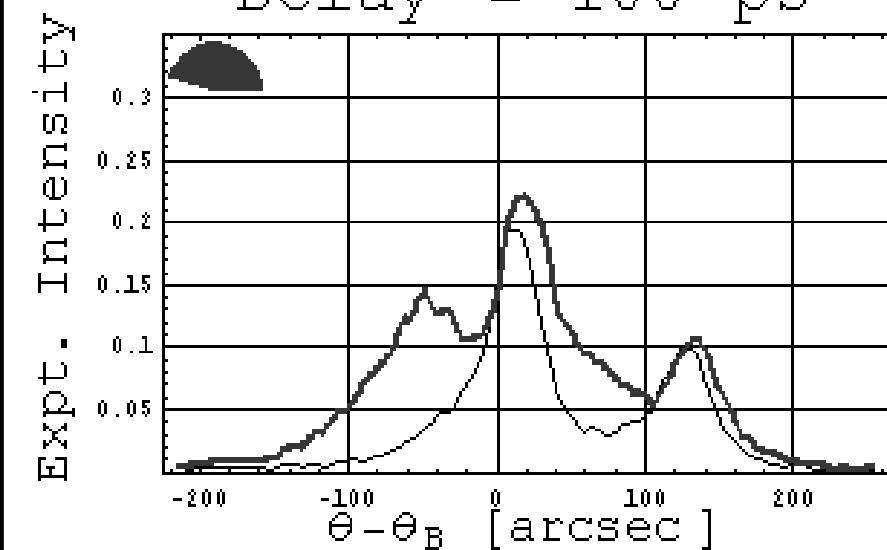
Diffraction Angle

$F = 50 \text{ mJ / cm}^2$

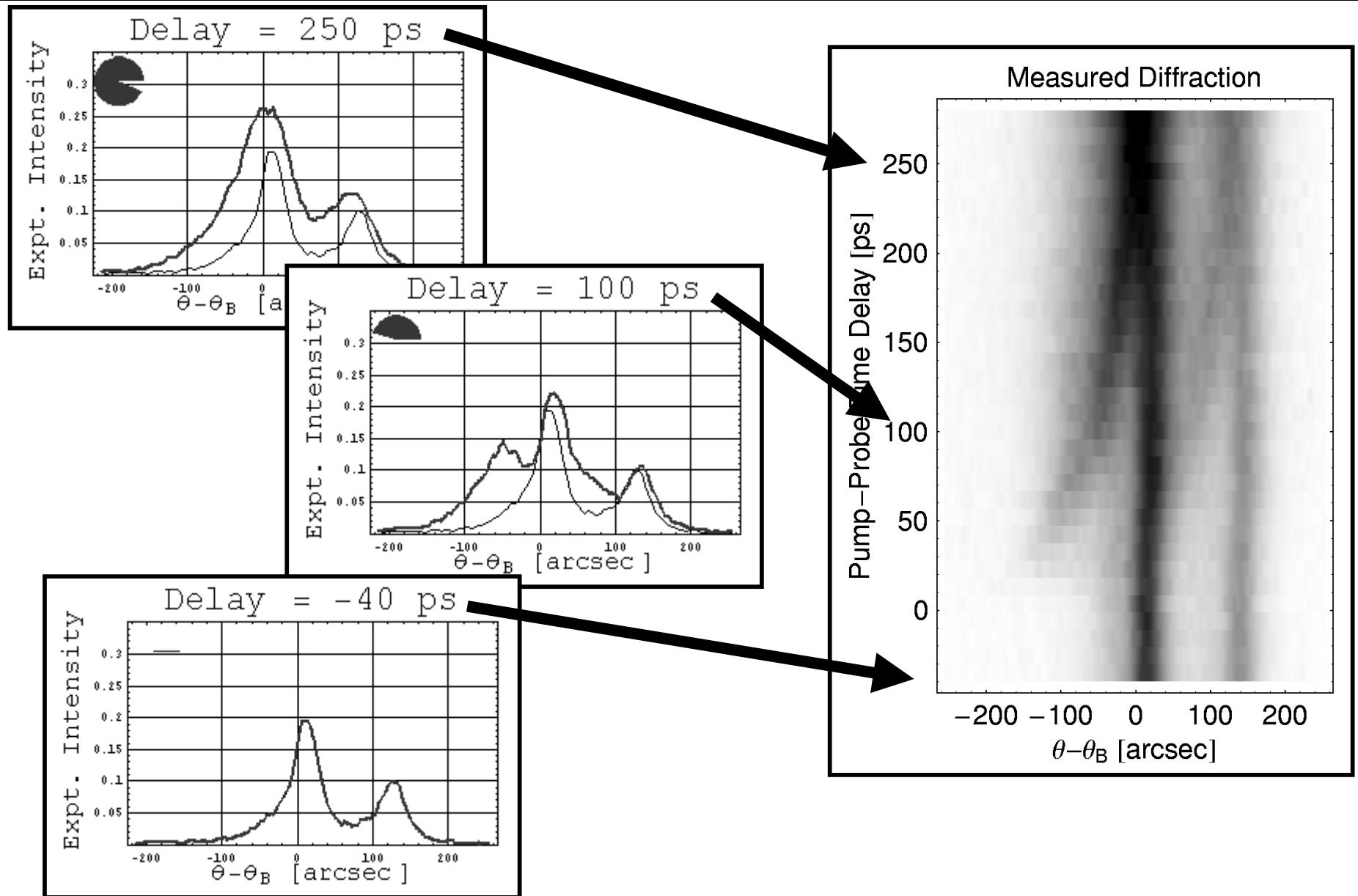
$\tau = 30 \text{ fs}$

Integrated Lineouts

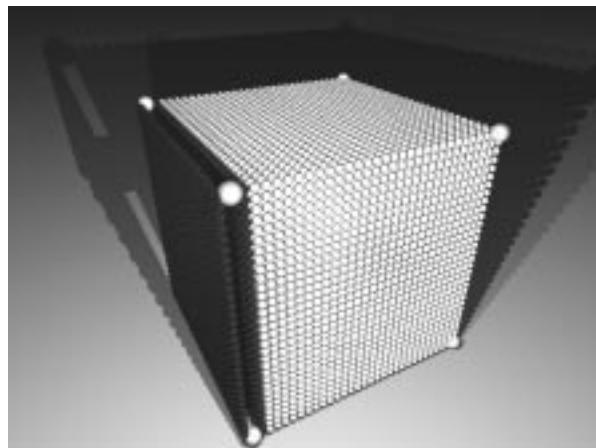
Delay = 100 ps



Ultrafast X-ray Diffraction: GaAs

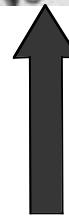
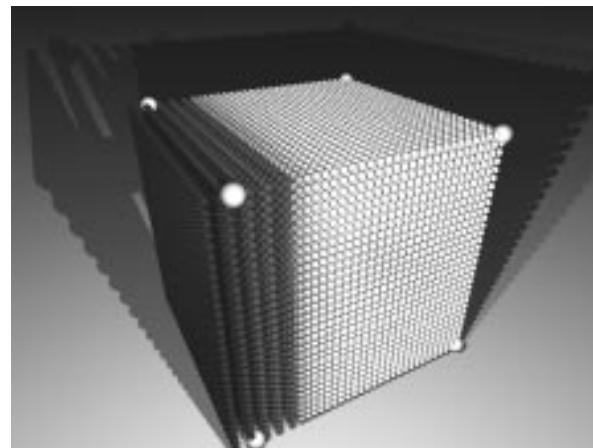


Coherent Acoustic Phonons



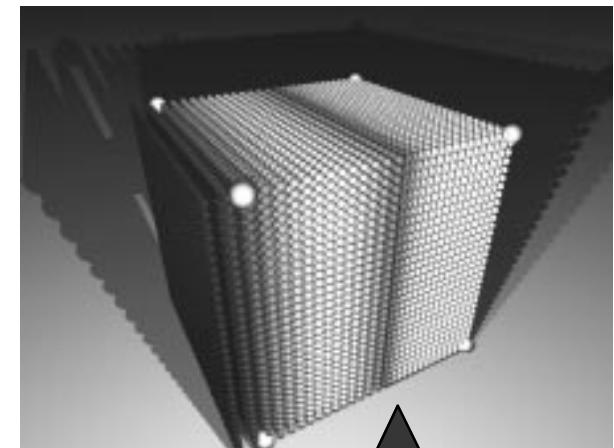
*Fast heating at
constant Volume*

Stress



Surface expansion

Strain

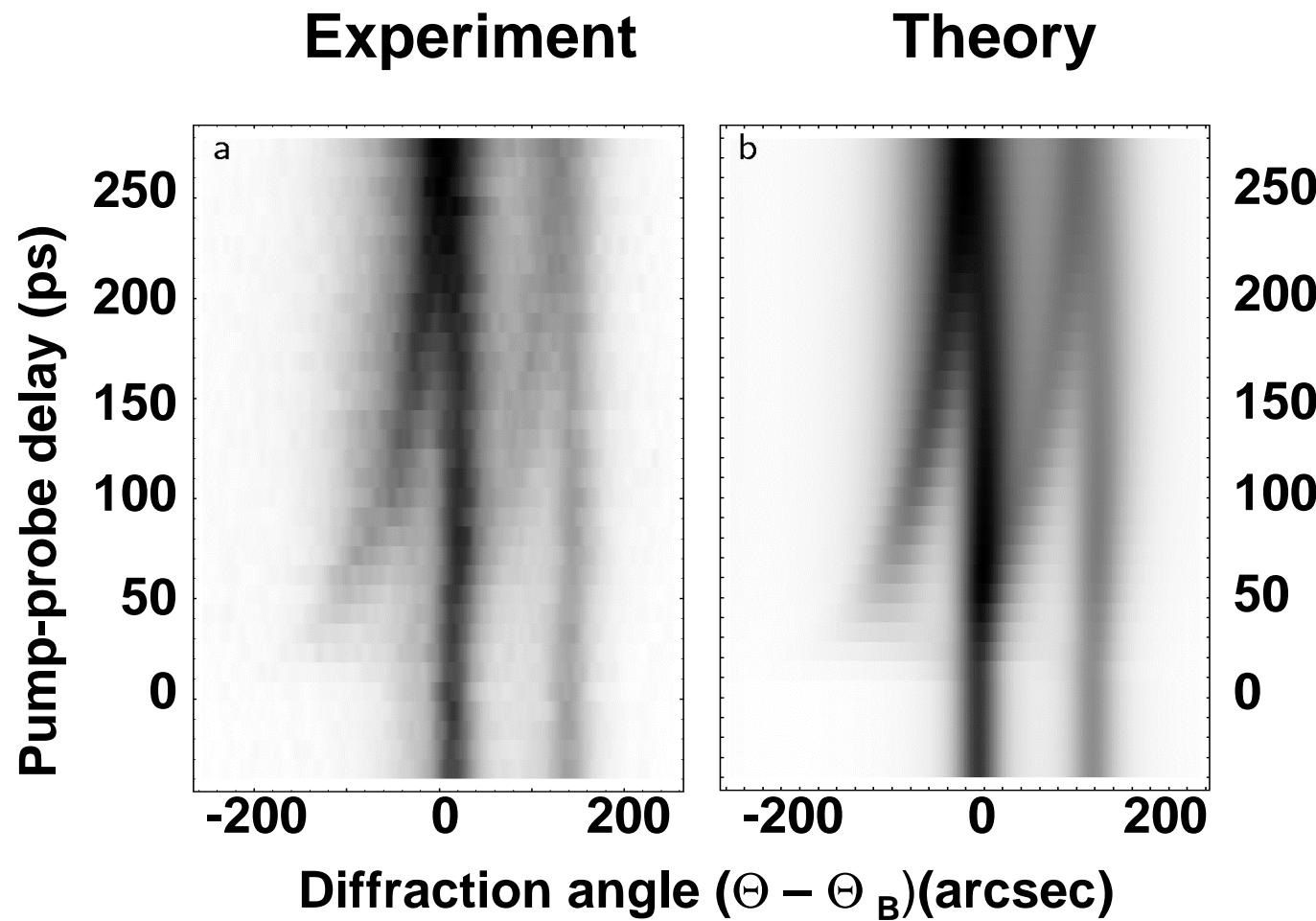


Newton's 3rd Law

**Acoustic
Pulse**

C. Thomsen et al. Phys Rev. B 34, 4129 (1986).

Gallium Arsenide



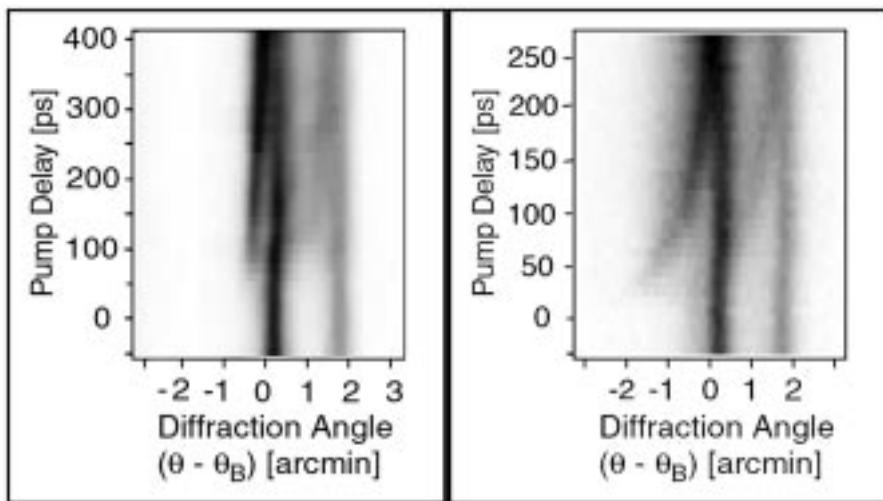
Ch. Rose-Petrucci et al. *Nature* 398, 310 (1999).

Heating depths



Experiment

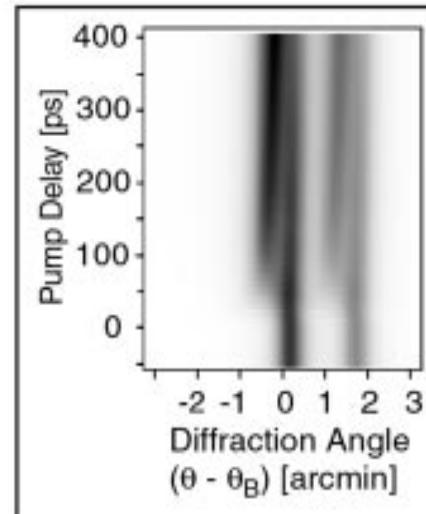
Ge



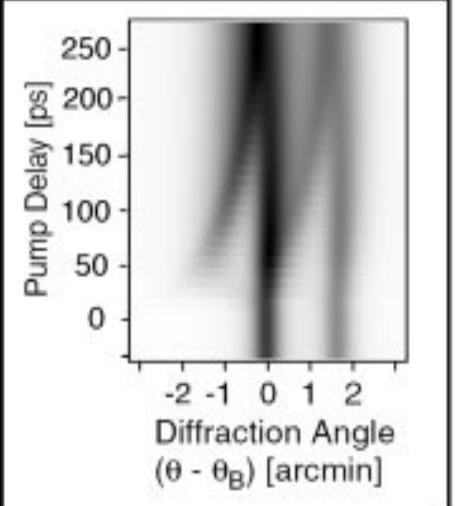
GaAs

Theory

Ge



GaAs



$$\zeta = 1 \mu m$$

$$\zeta = 275 \mu m$$

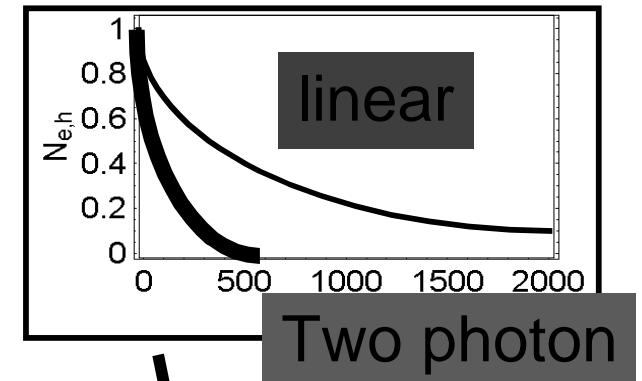
Heating depths



Two-temperature model

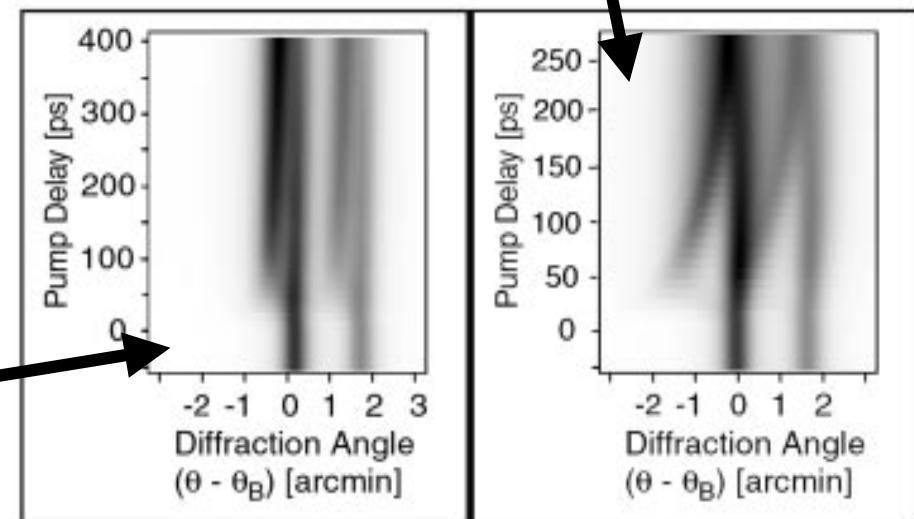
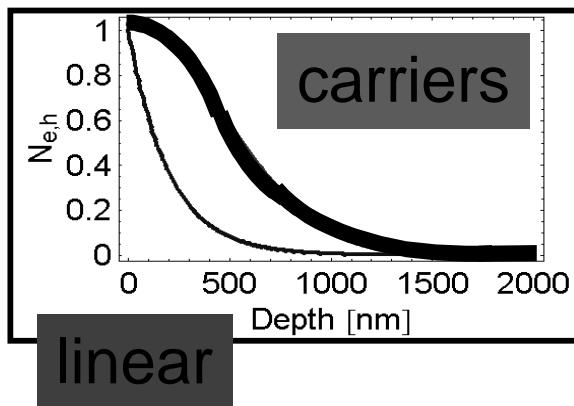
- ✓ Two photon absorption
- ✓ High density carrier diffusion
- ✓ Auger recombination coefficients

GaAs

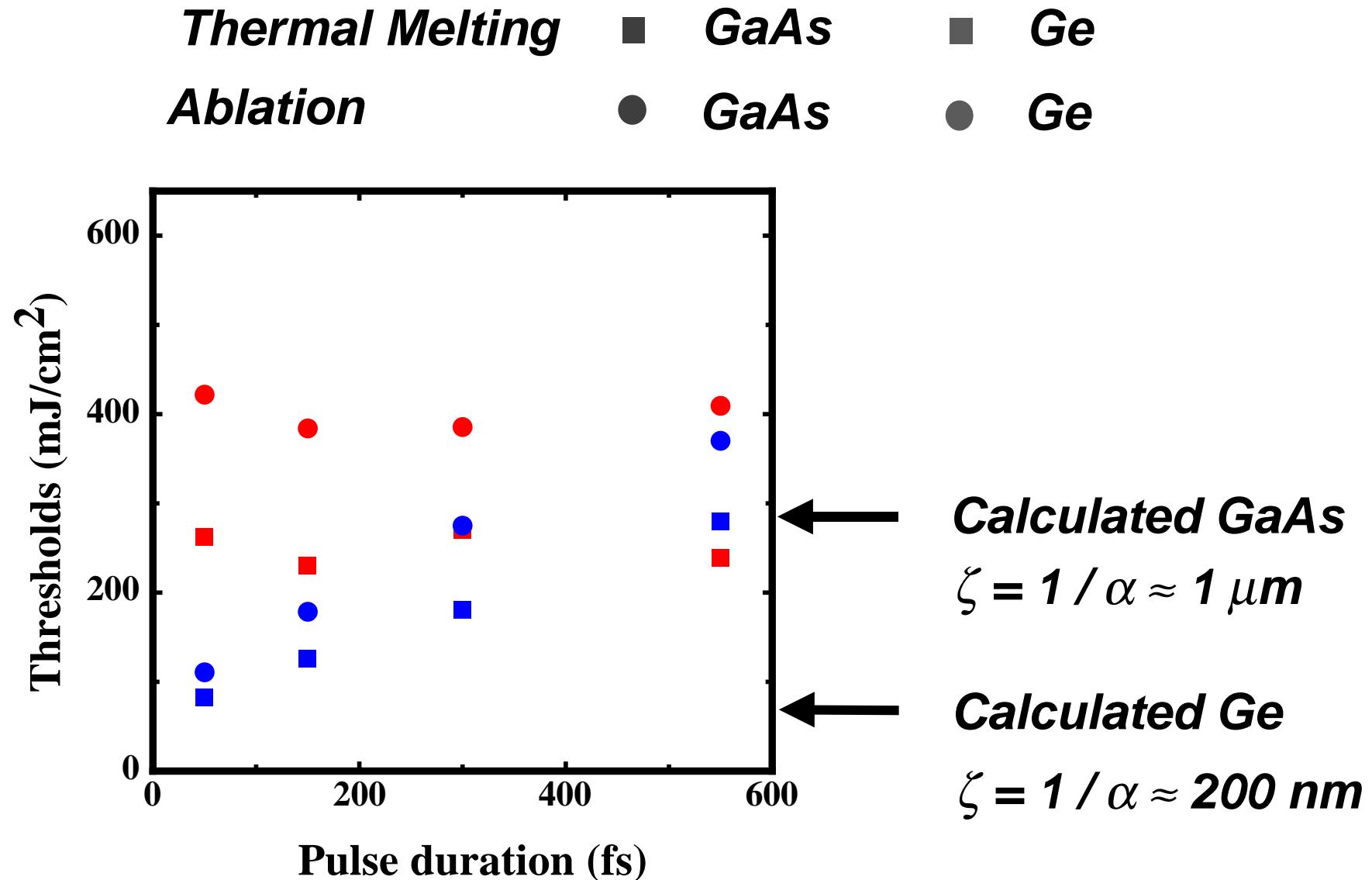


Two photon

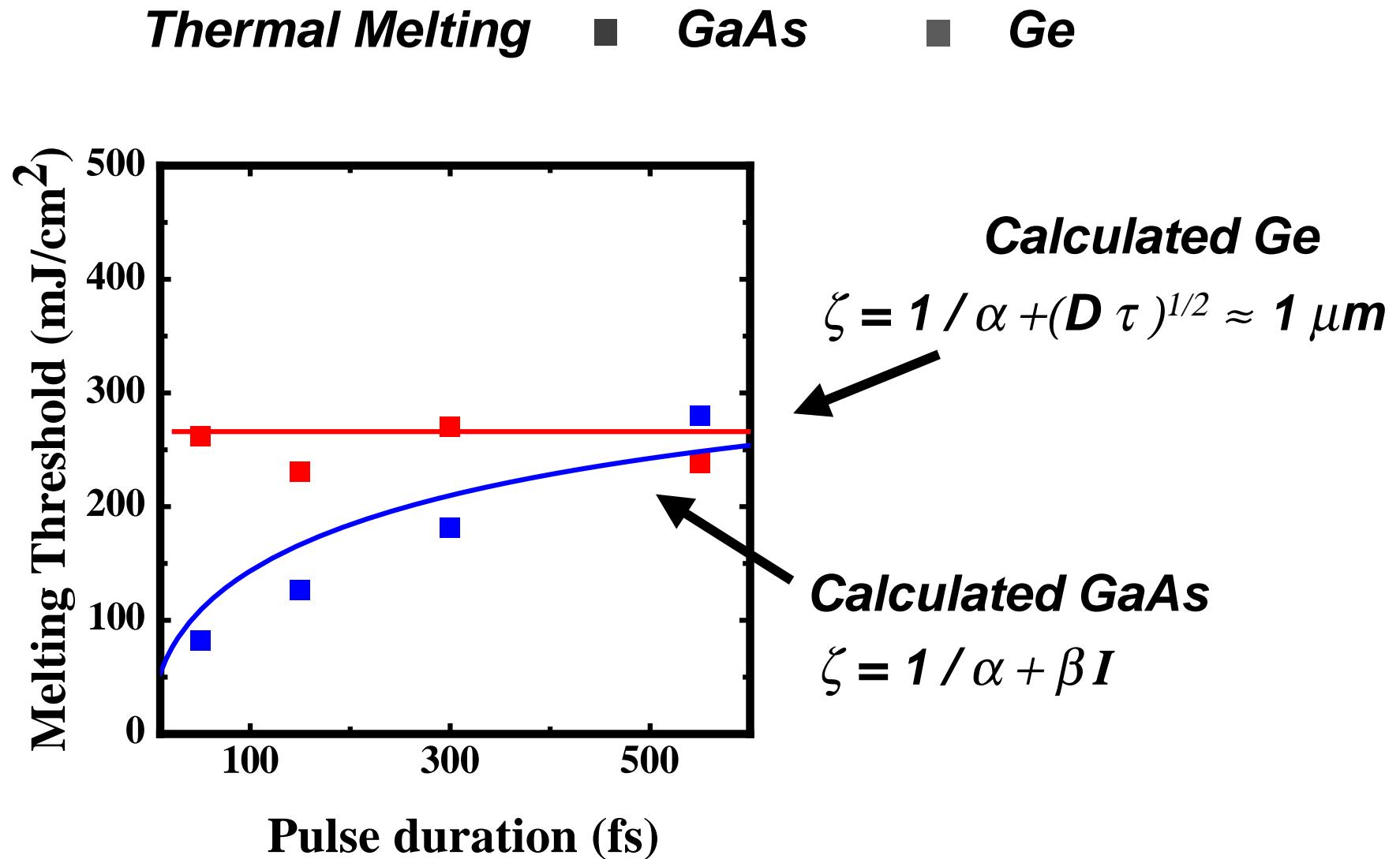
Ge



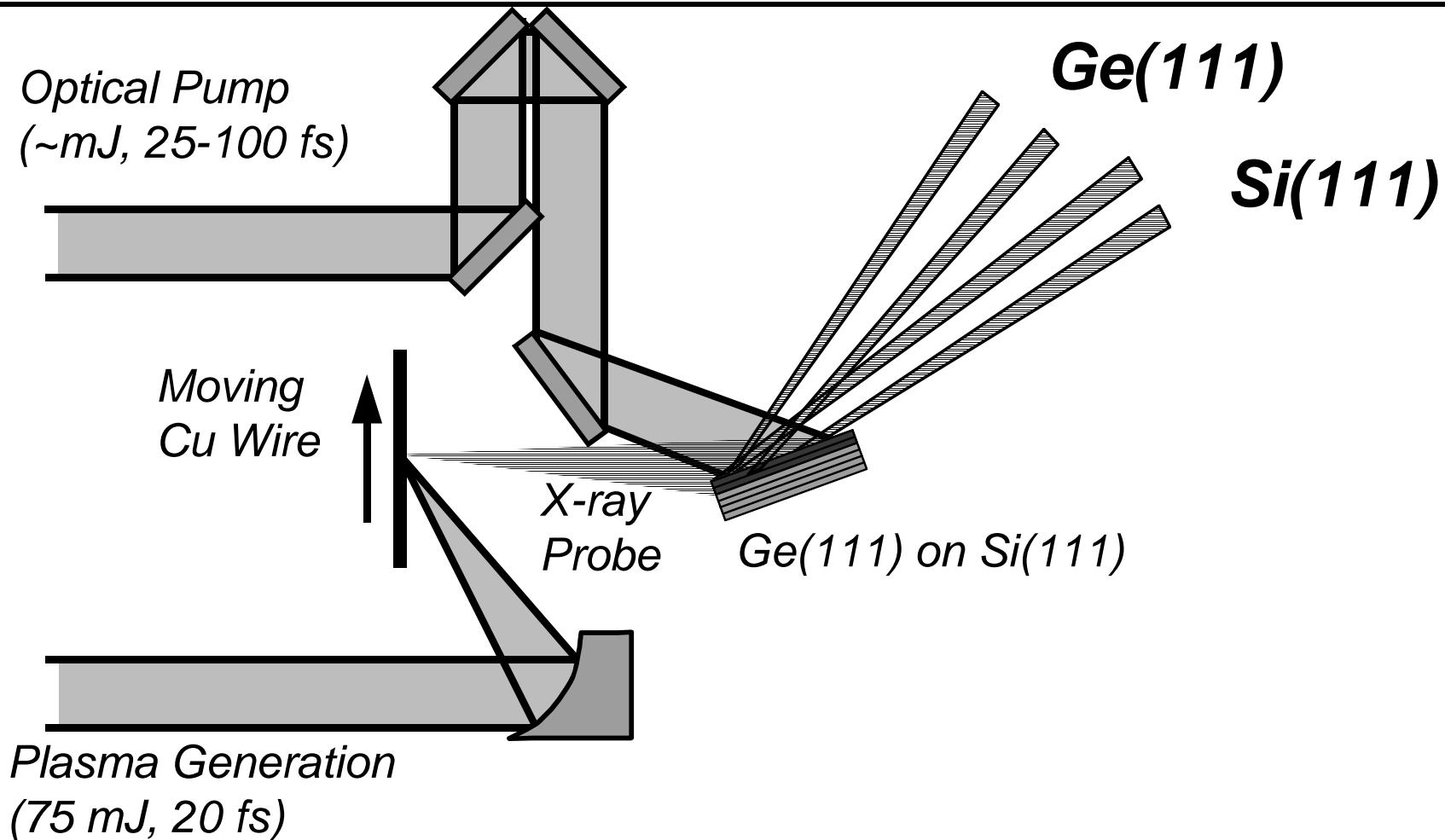
Dependence on pulse duration



Dependence on pulse duration



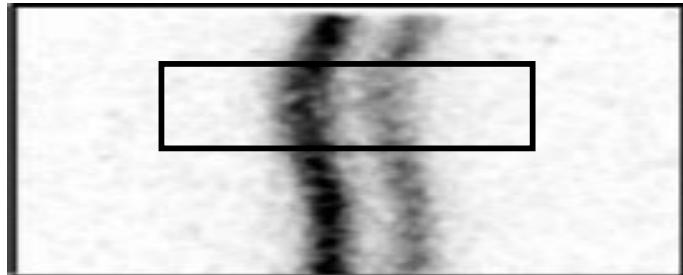
Probing Hetero-structures



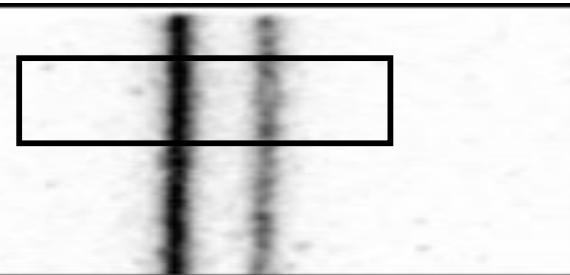
Centroid positions (400 nm film)



Ge

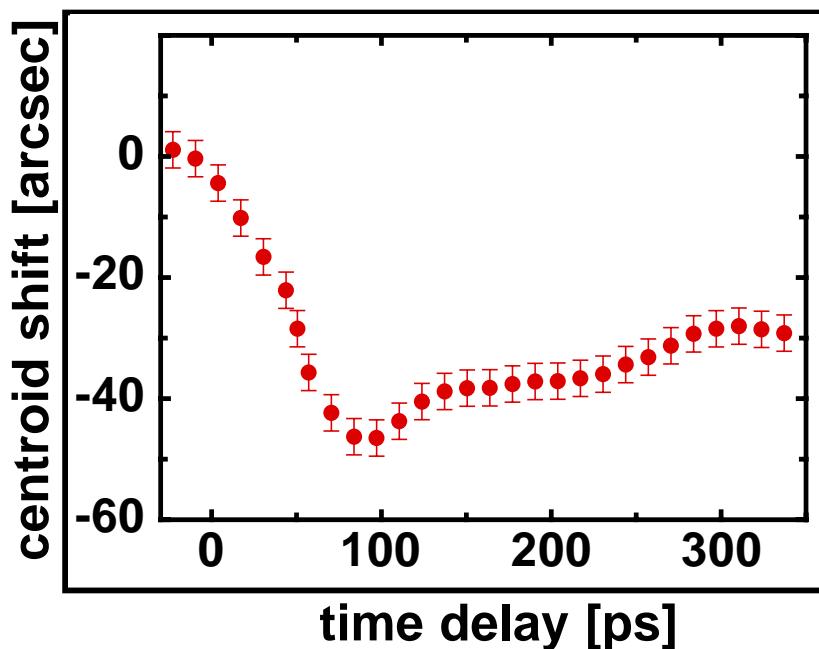


Si

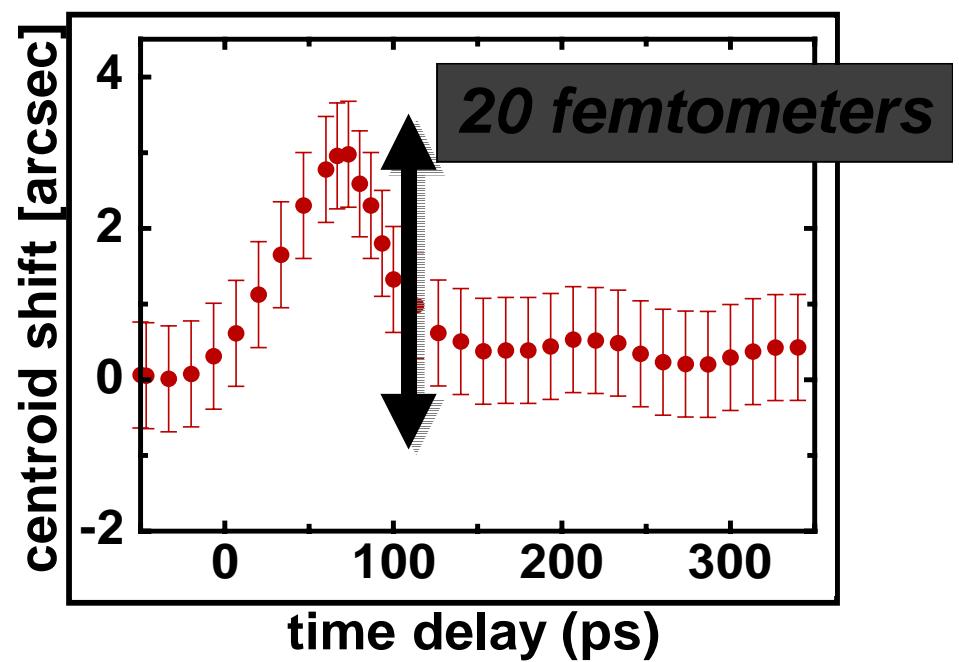


$$\tau_{\text{delay}} = 100 \text{ ps}$$

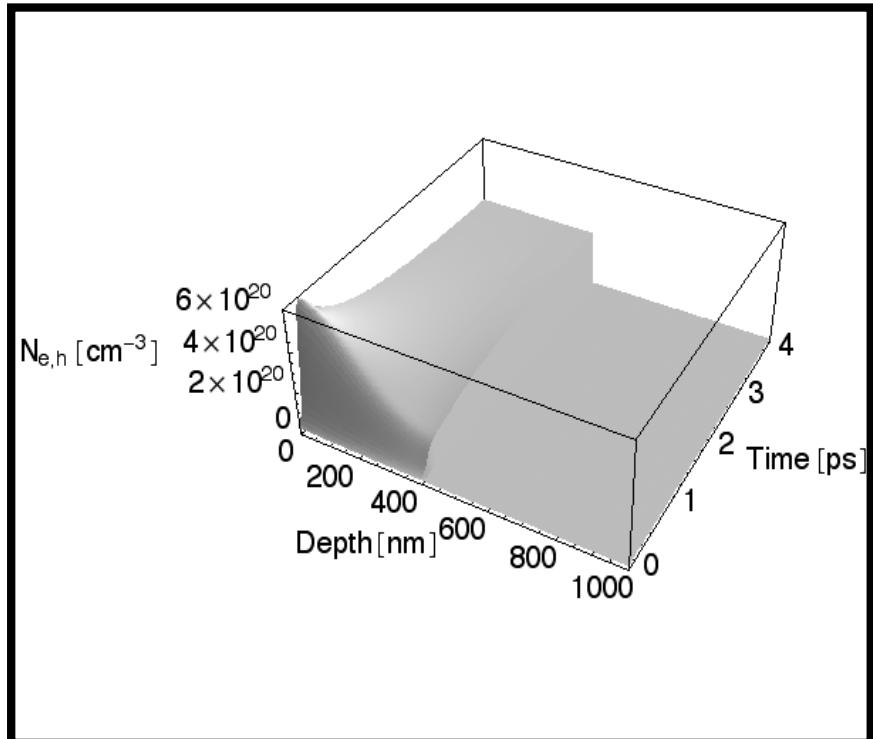
Expansion



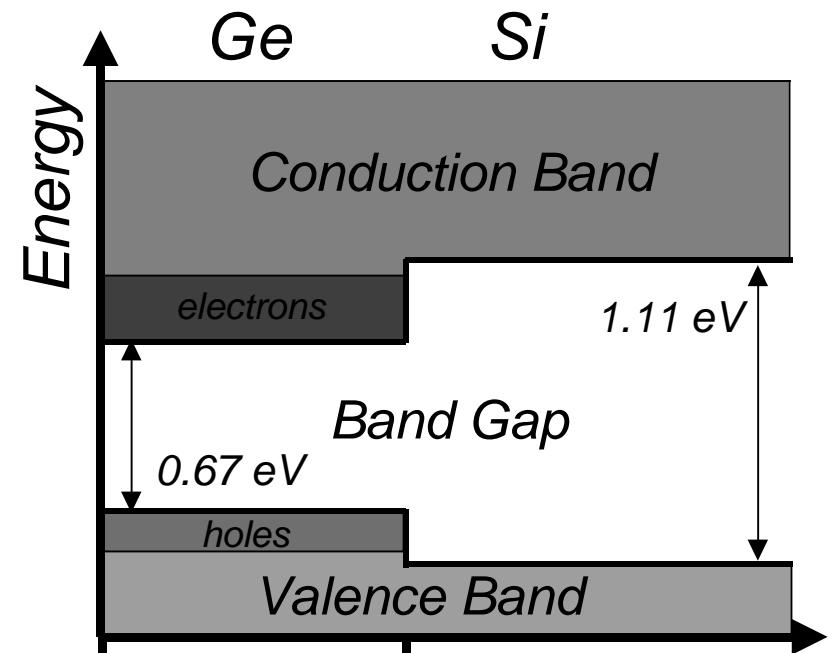
Compression



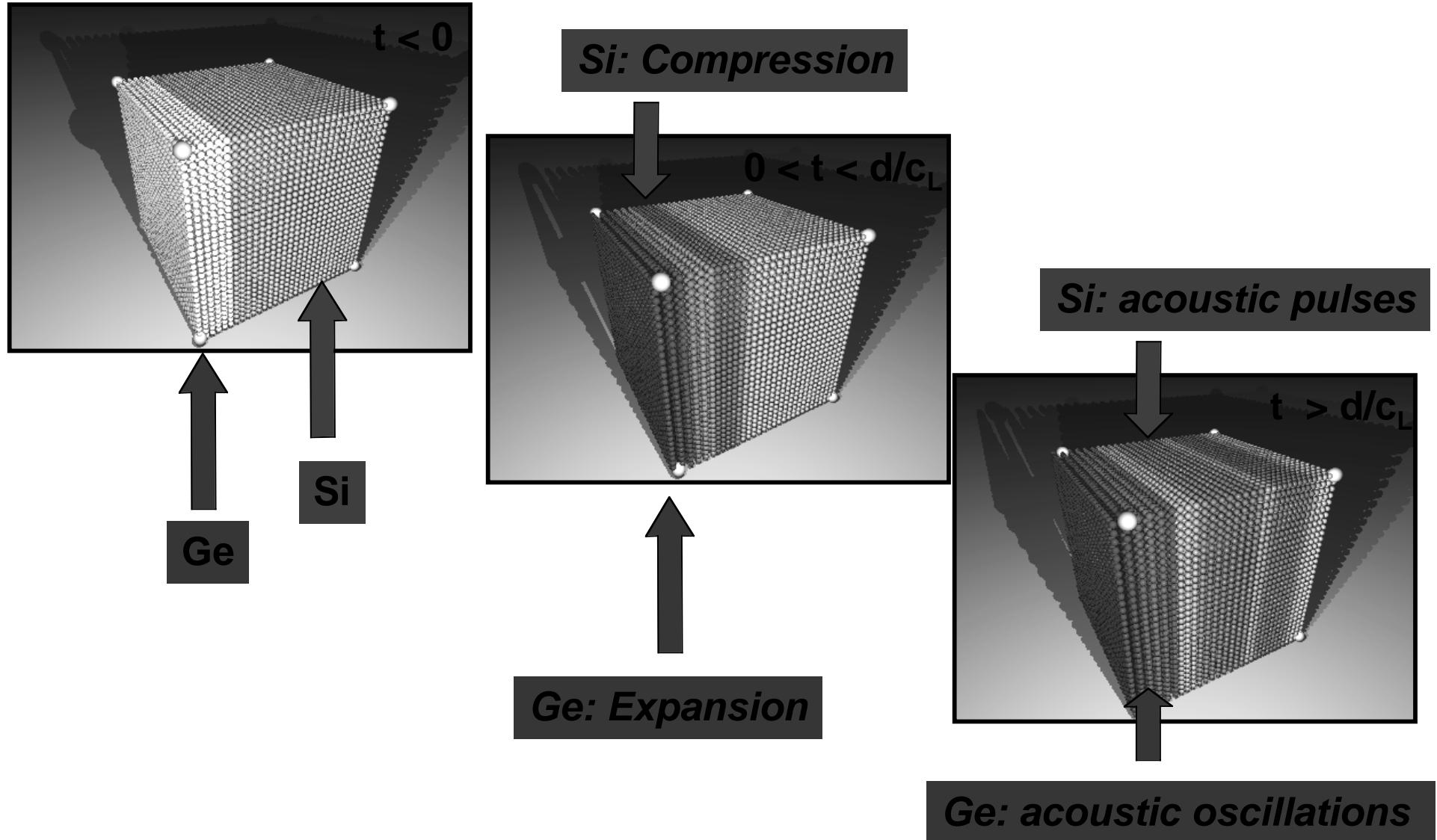
Carrier dynamics (400 nm)



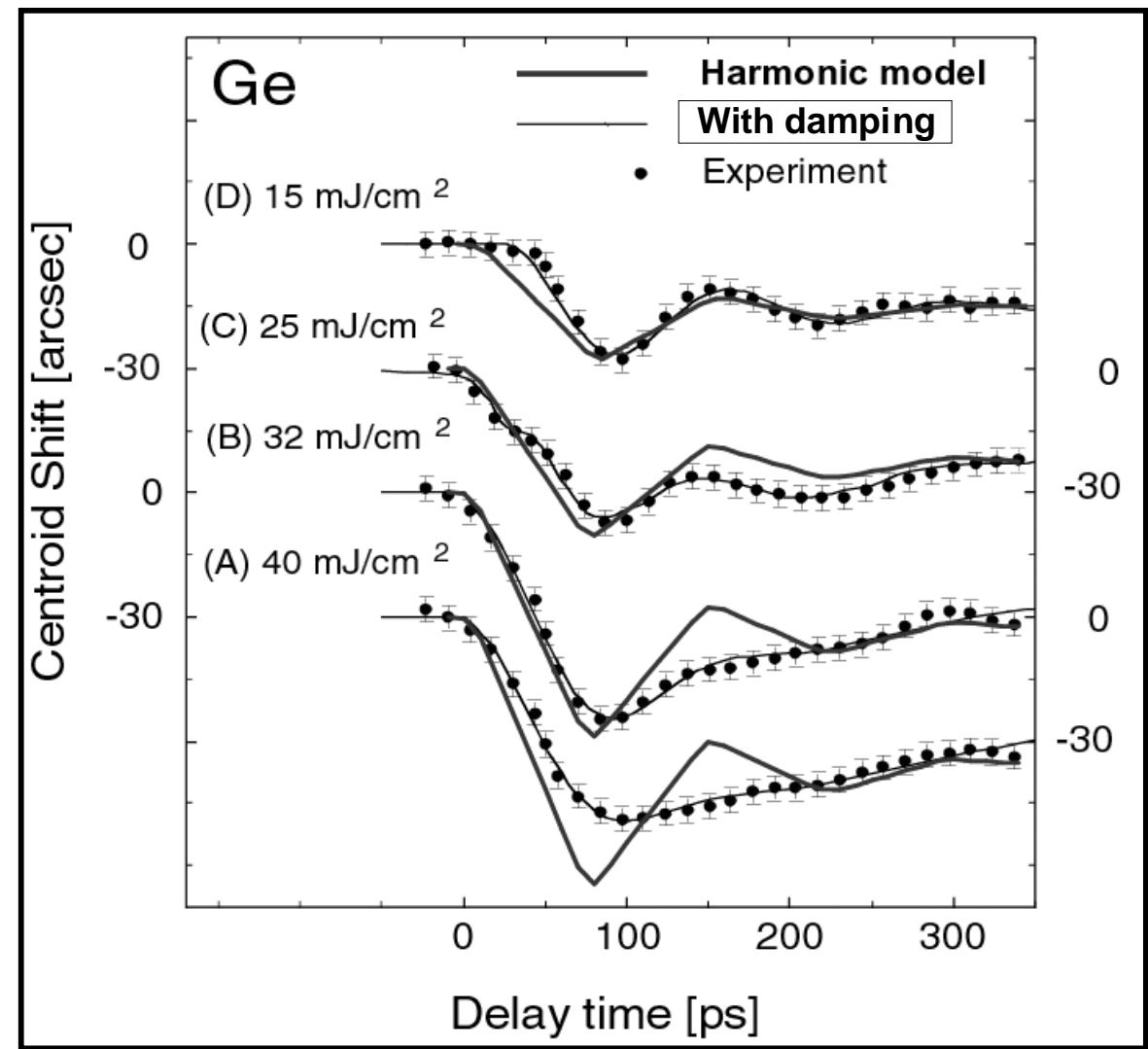
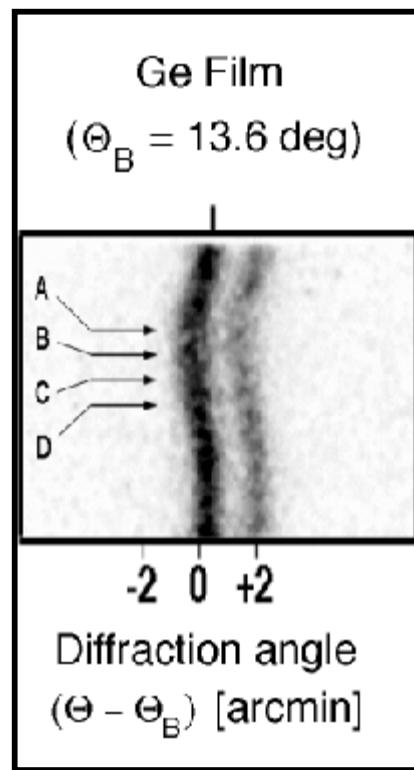
- ✓ Only Ge absorbs
- ✓ Carrier diffusion
- ✓ Carriers are confined



Coherent Acoustic Phonons: Films



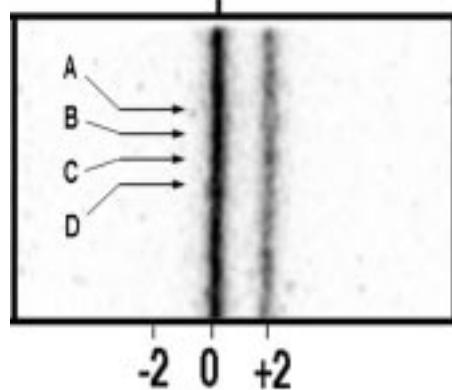
Fluence Dependent Damping



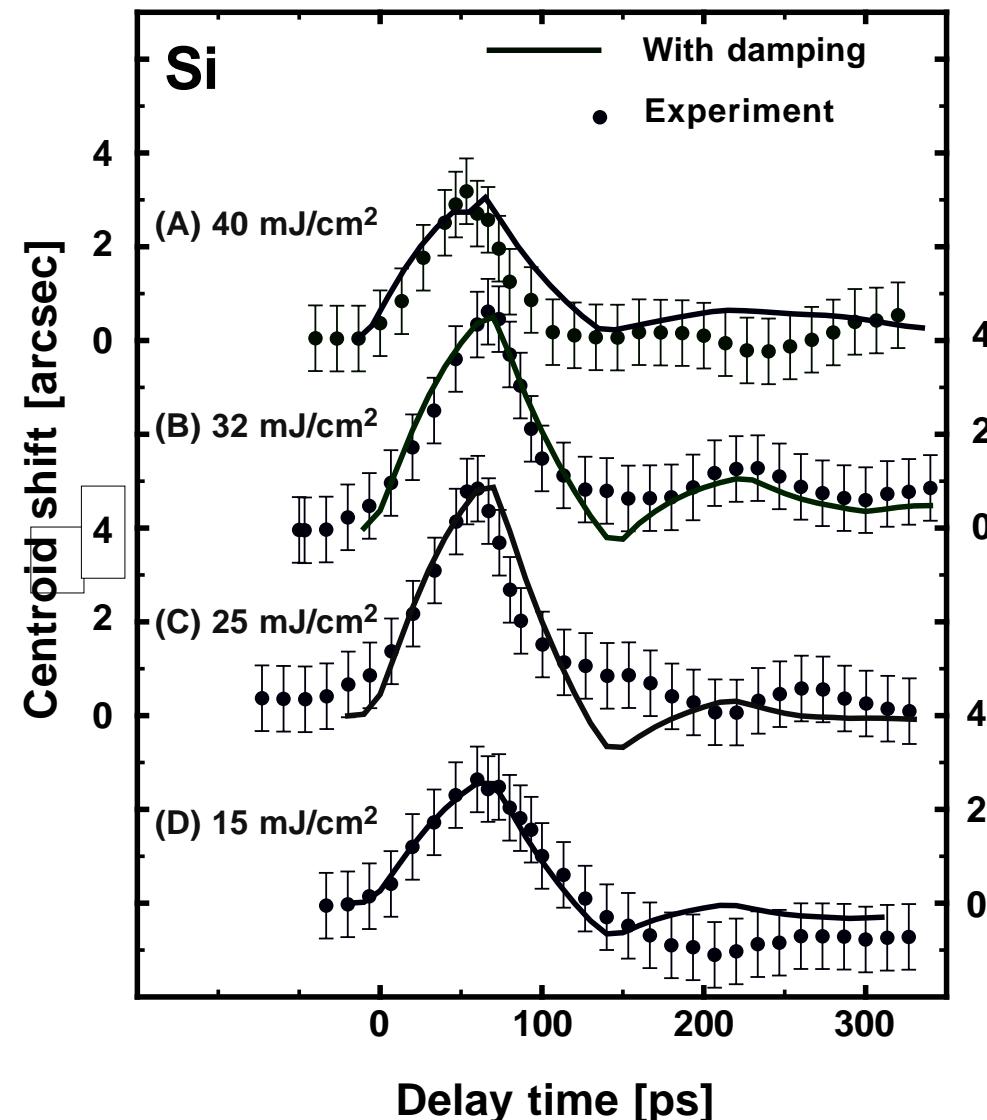
Fluence Dependent Damping



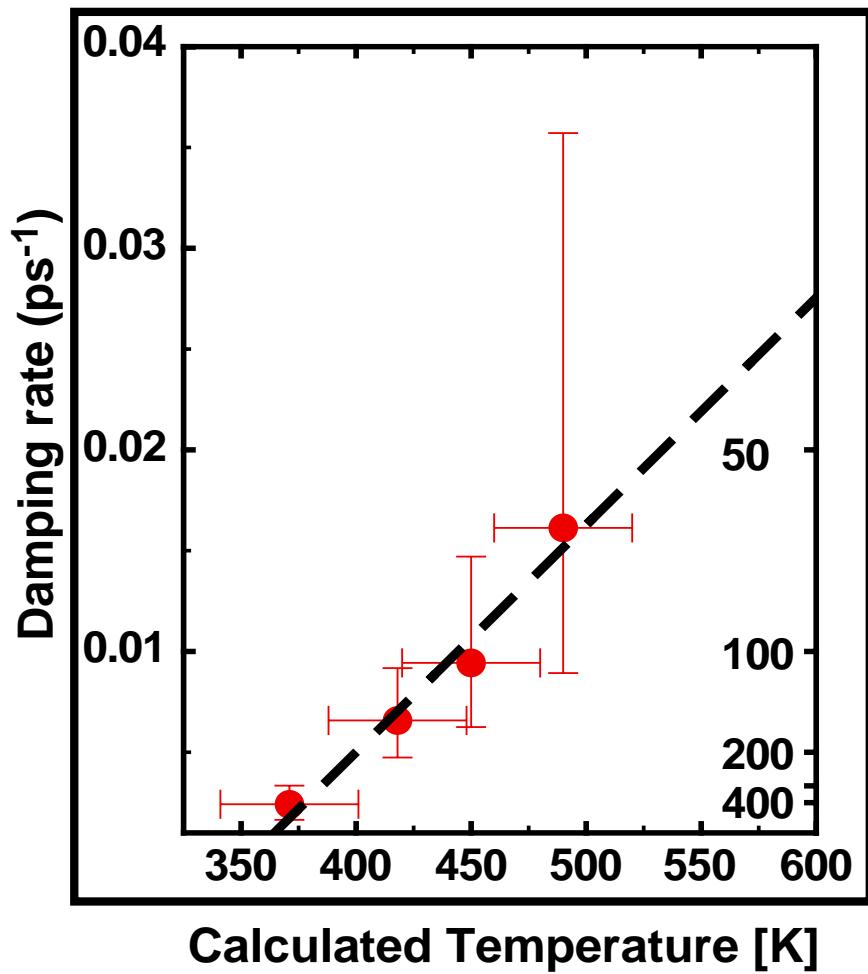
Si Substrate
 $(\Theta_B = 14.2 \text{ deg})$



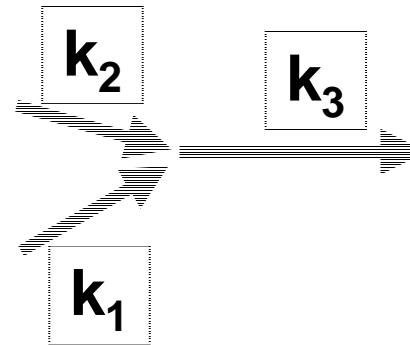
Diffraction angle
 $(\Theta - \Theta_B)$ [arcmin]



Coherent Phonon Damping Times

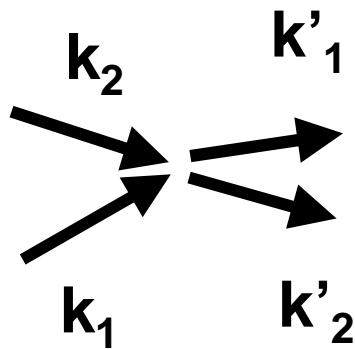


Phonon collision



$T_1 \sim 100$ ns

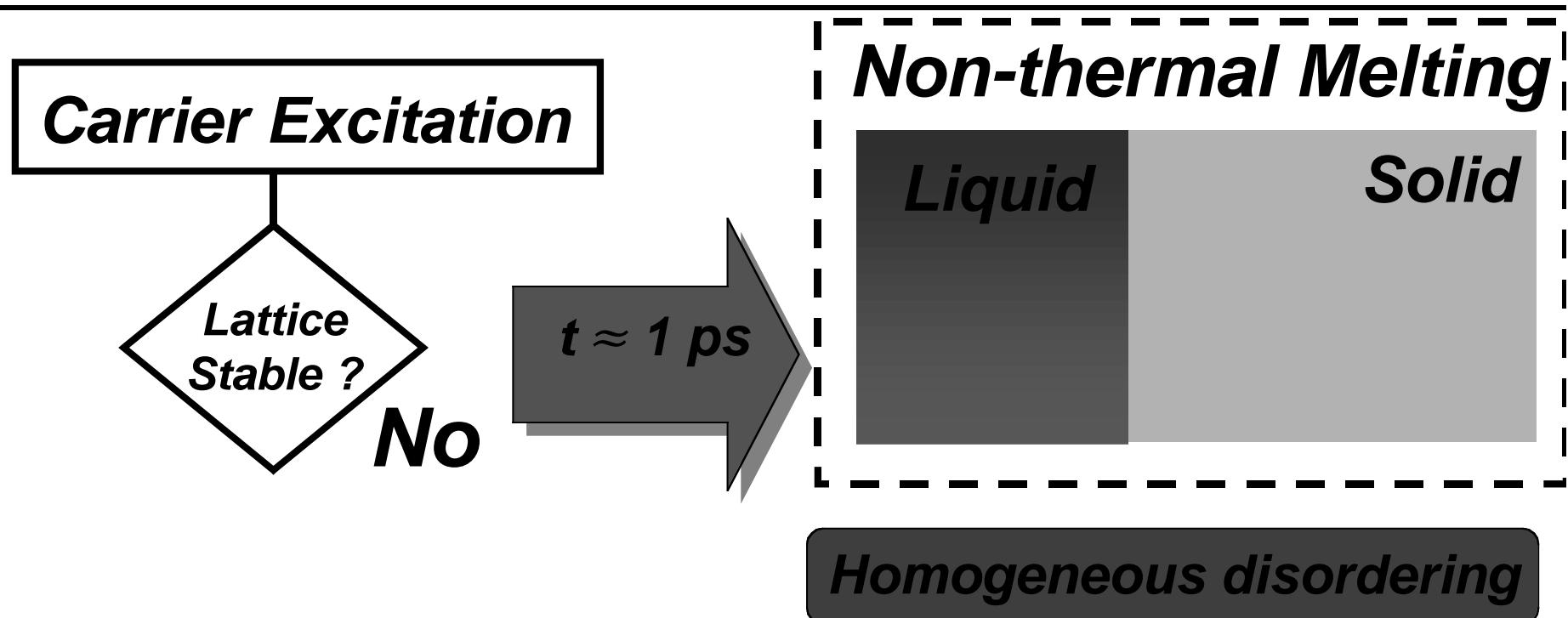
Phonon dephasing



$T_2 \sim 100$ ps

A. Cavalleri et al., *Phys. Rev. Lett.* 85, 586 (2000)

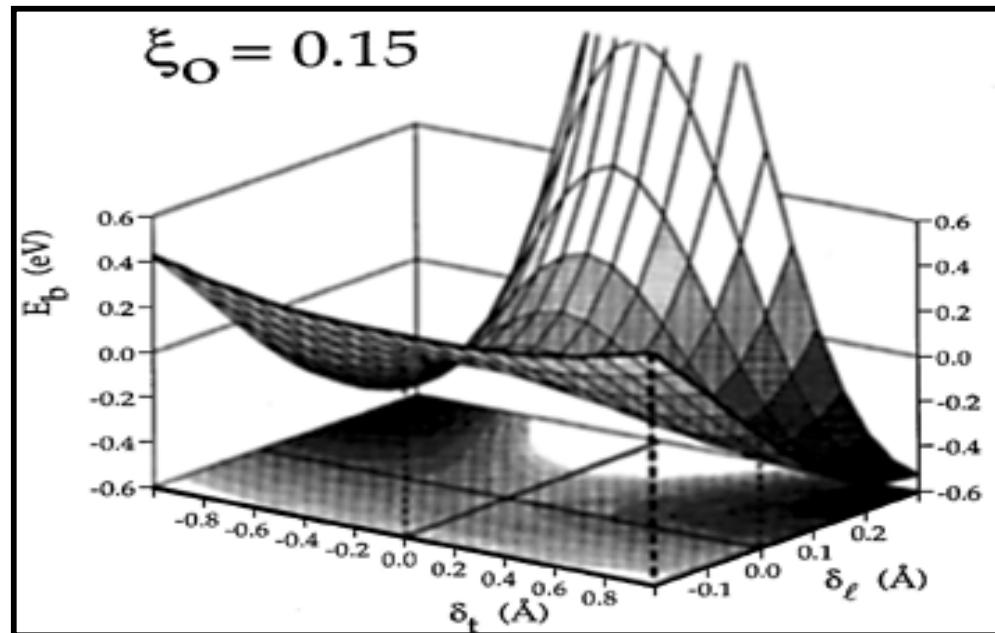
Ultrafast Melting Dynamics



J.A. van Vechten et al., *Phys. Lett. A* 74A, 422 (1979).

P.L. Silvestrelli et al., *Phys. Rev. Lett.* 77, 3149 (1996).

Potential Energy Surface

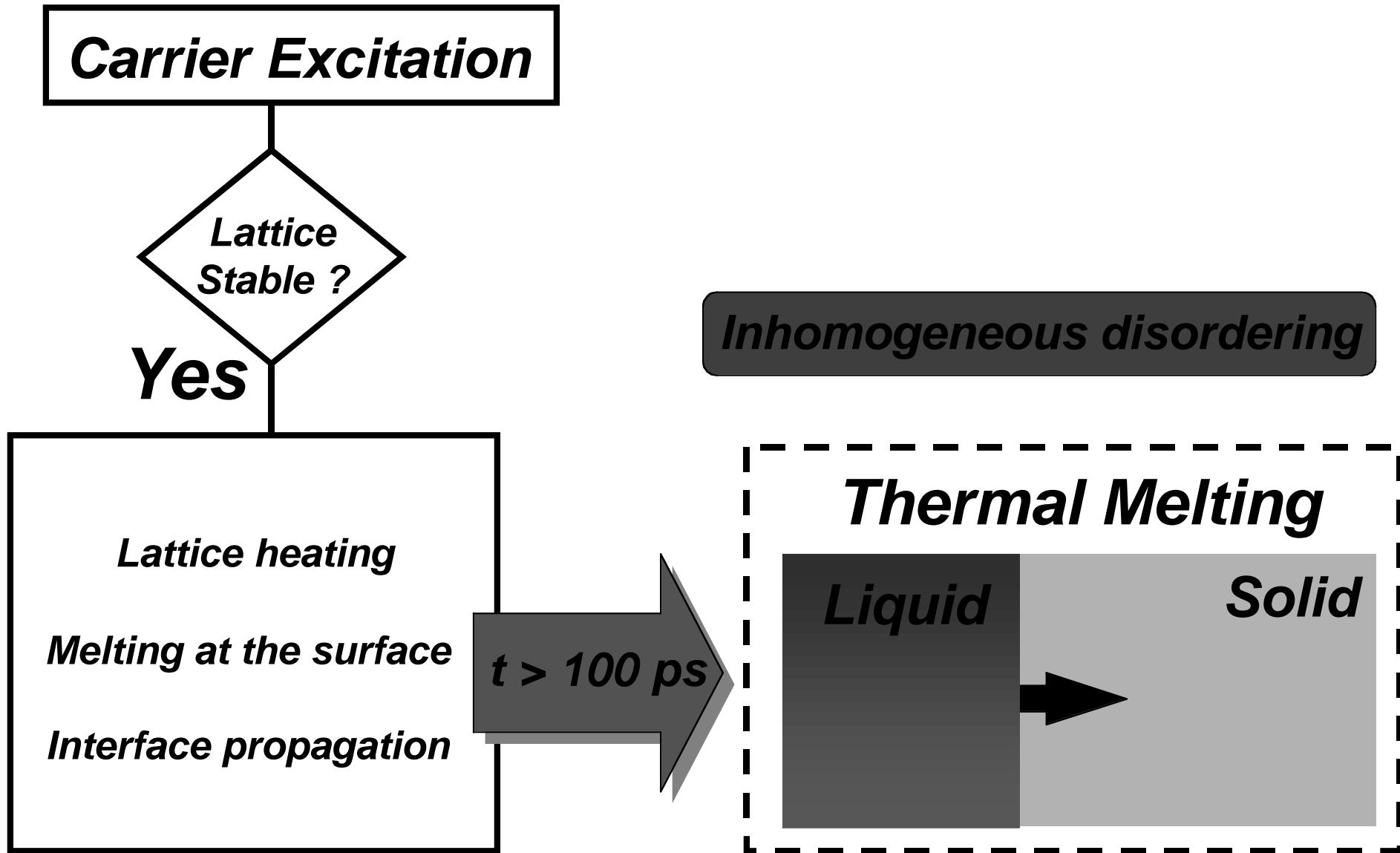


10^{22} excited carriers/cm³

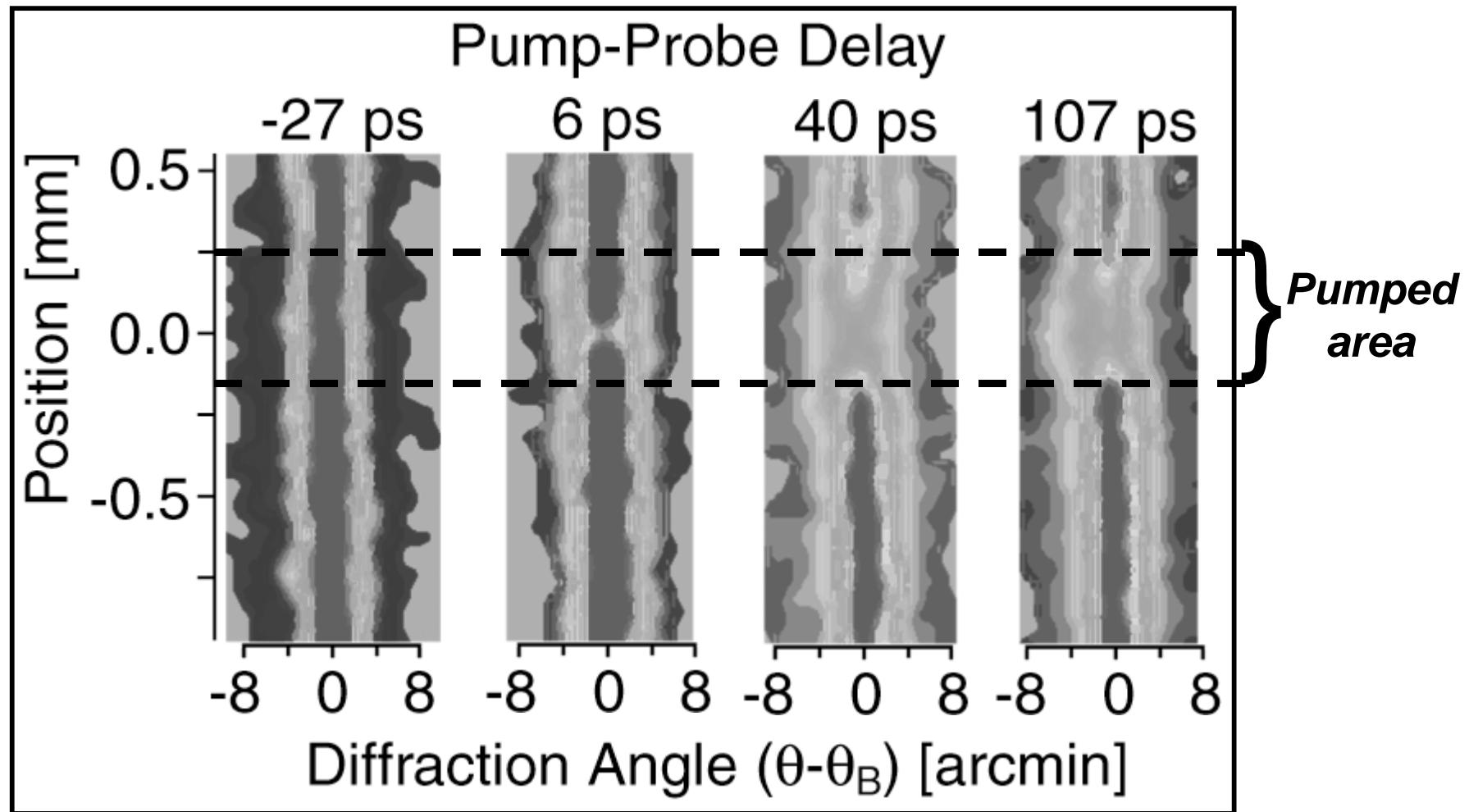
**25% valence electrons
in the conduction band**

Unstable lattice

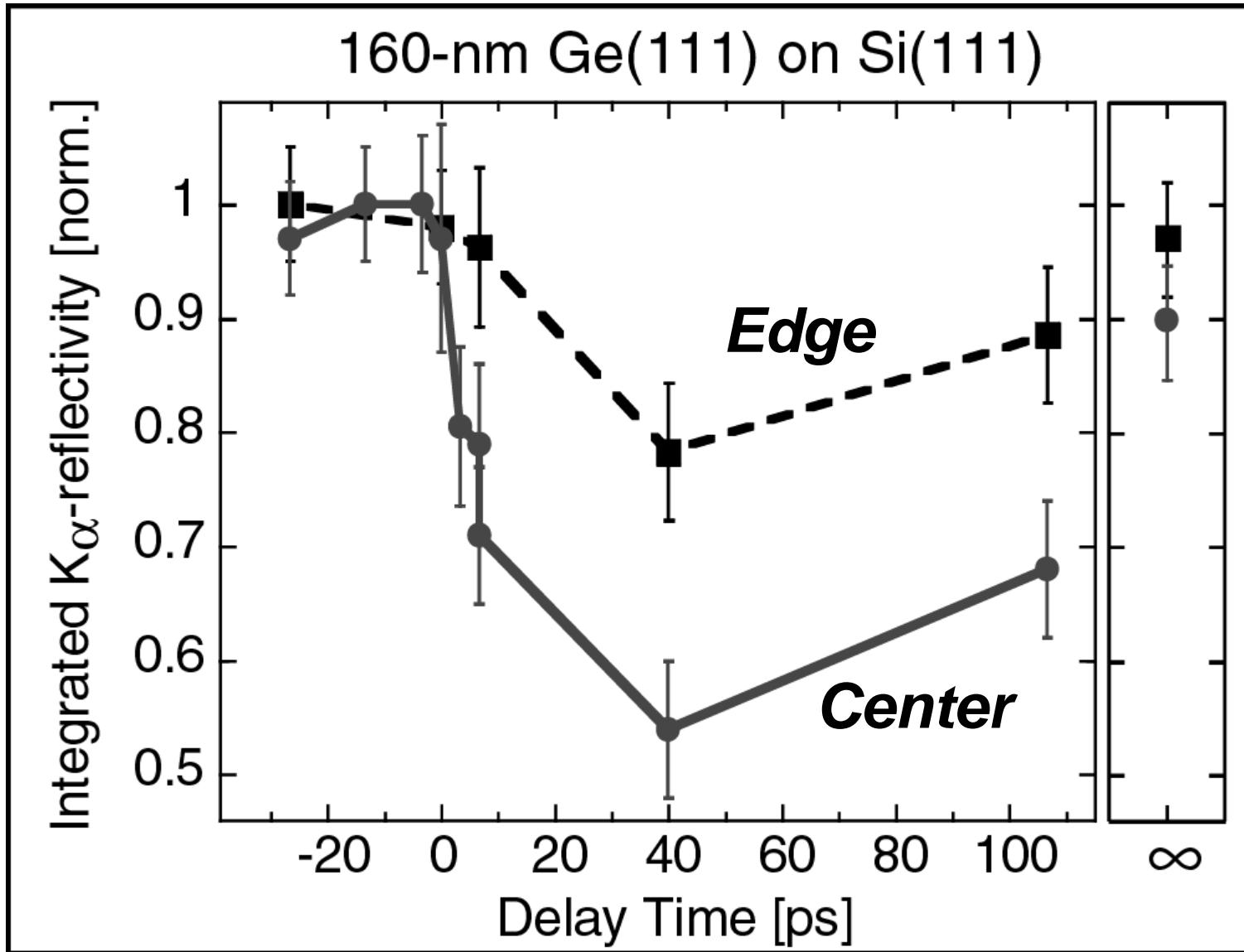
Ultrafast Melting Dynamics



Ultrafast Melting in 160 nm Ge



Ultrafast Melting: Integrated K_{α} Reflectivity



Ultrafast Melting



160 nm

40 nm in < 7 ps



**Homogeneous
Disordering**



Ge (111)

Si (111)

Ultrafast Melting

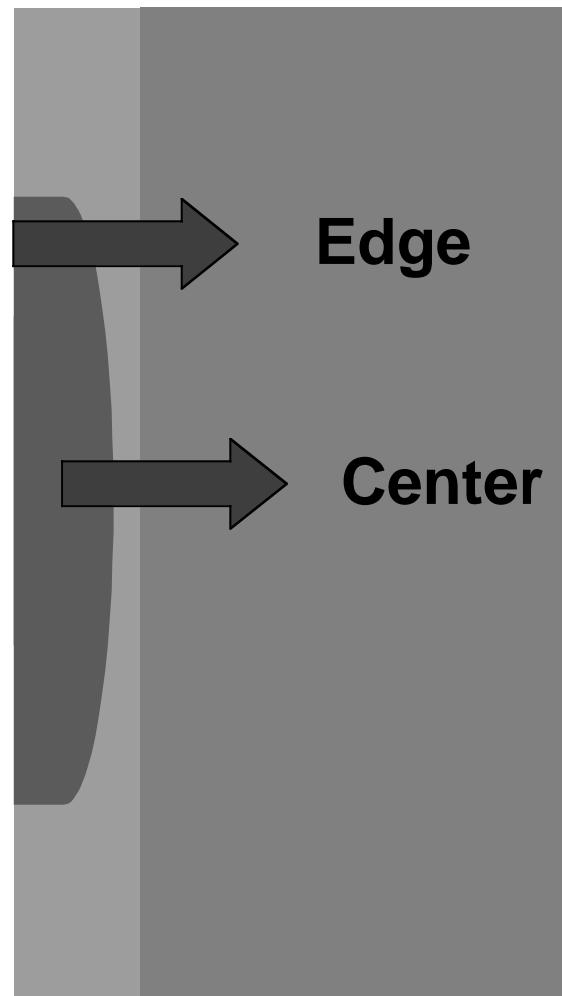


160 nm

Inhomogeneous

Highly superheated solid

Interface velocity
 $V < 700 \text{ m / sec}$



Ge (111)

Si (111)

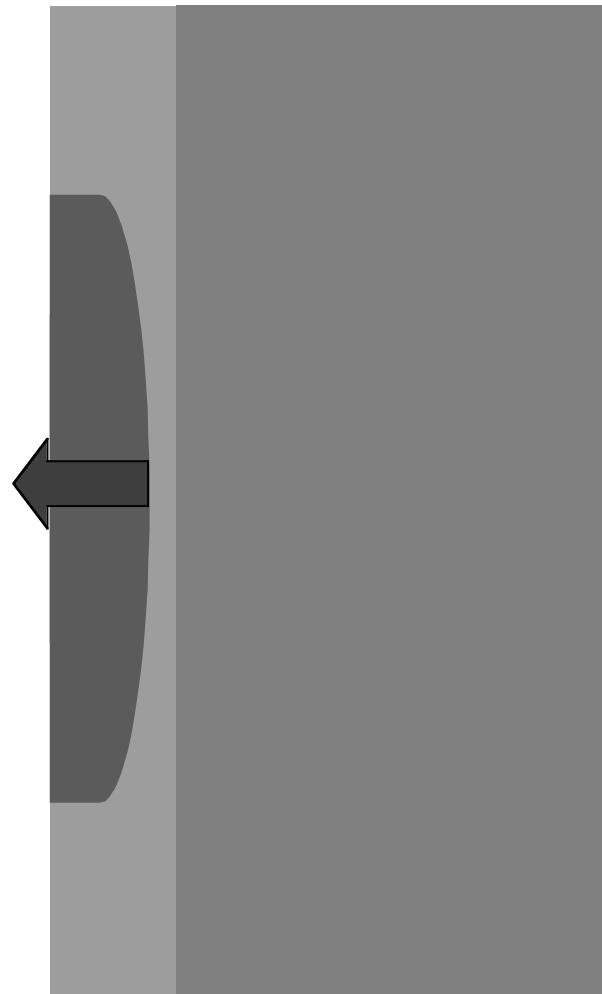
Ultrafast Melting



160 nm

Re-solidification

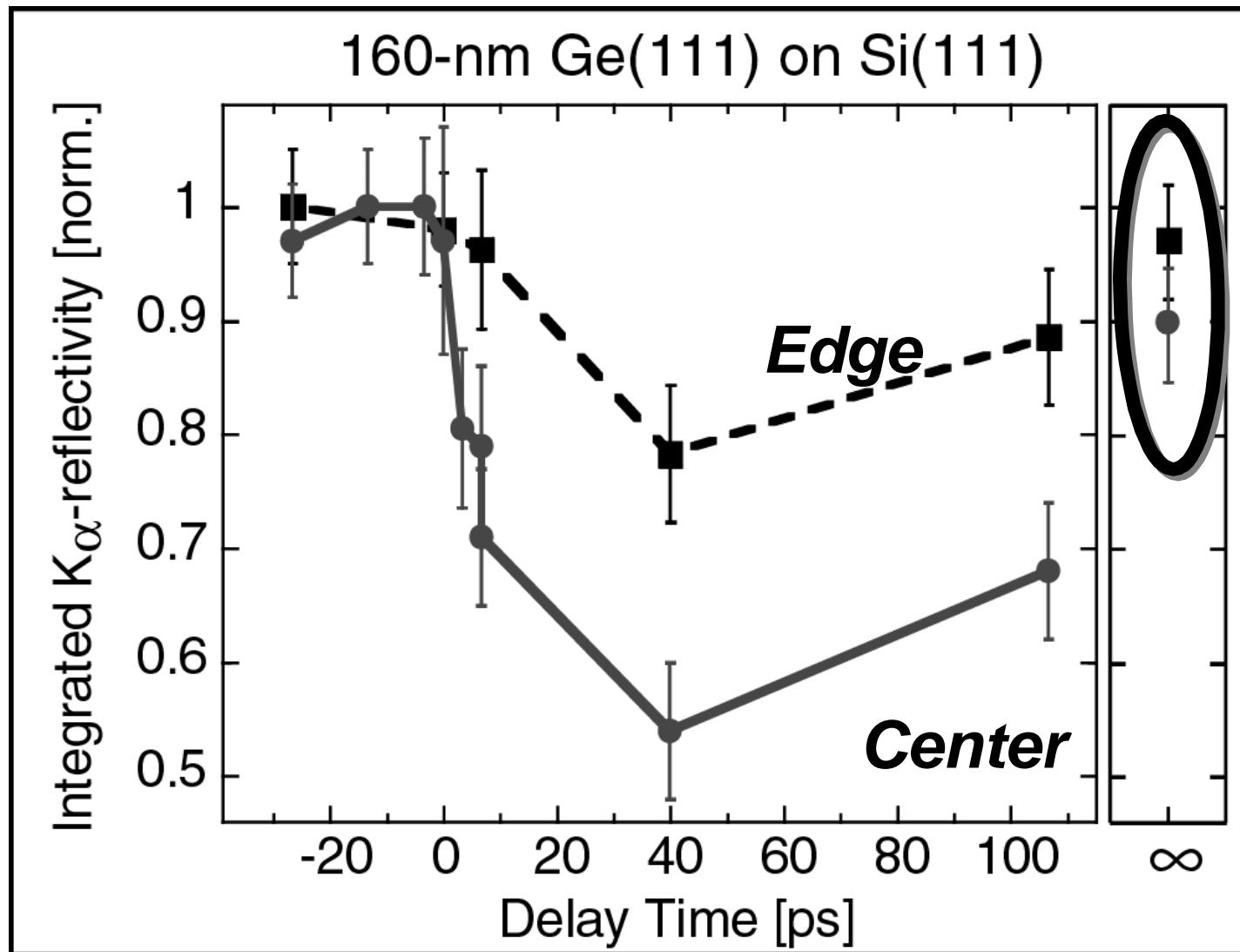
Solid-liquid-solid



Ge (111)

Si (111)

Ultrafast Melting: Integrated K_{α} Reflectivity

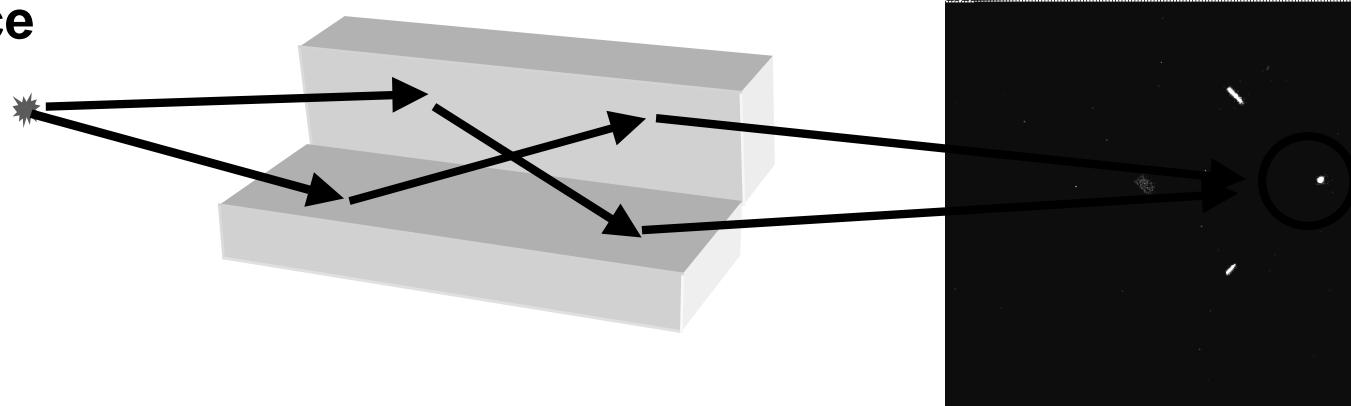


X-ray Focusing



Elliptical surfaces with graded Bragg coating

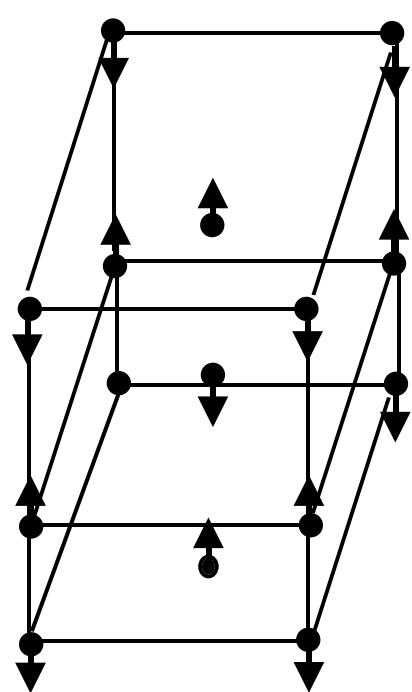
X-ray source



Spot diameter = $54 \mu\text{m}$

2000 photons / shot

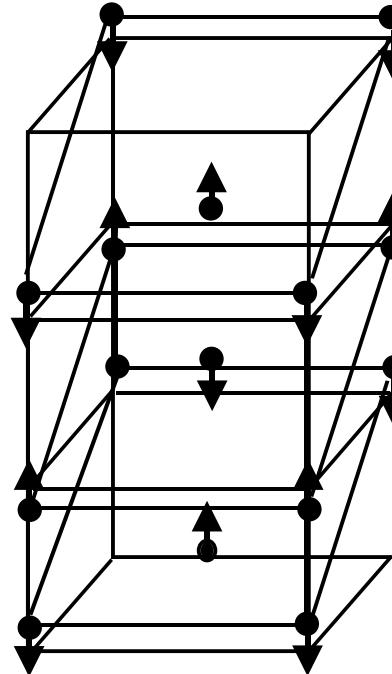
Structural Transition



$T < 340 \text{ K}$

Monoclinic

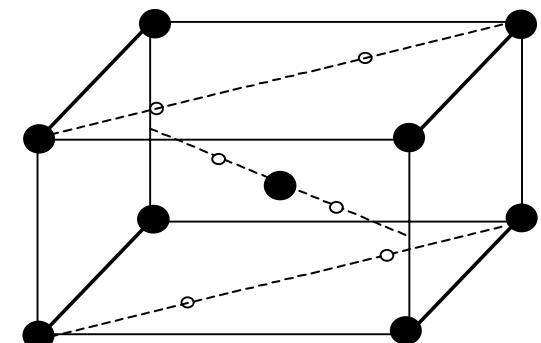
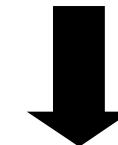
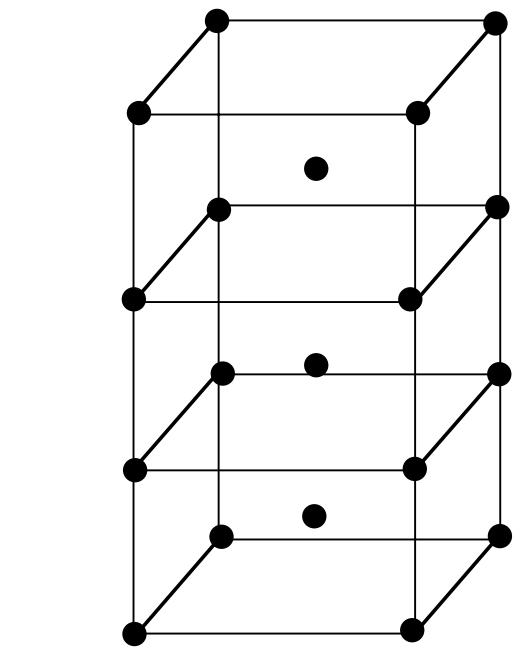
Insulator



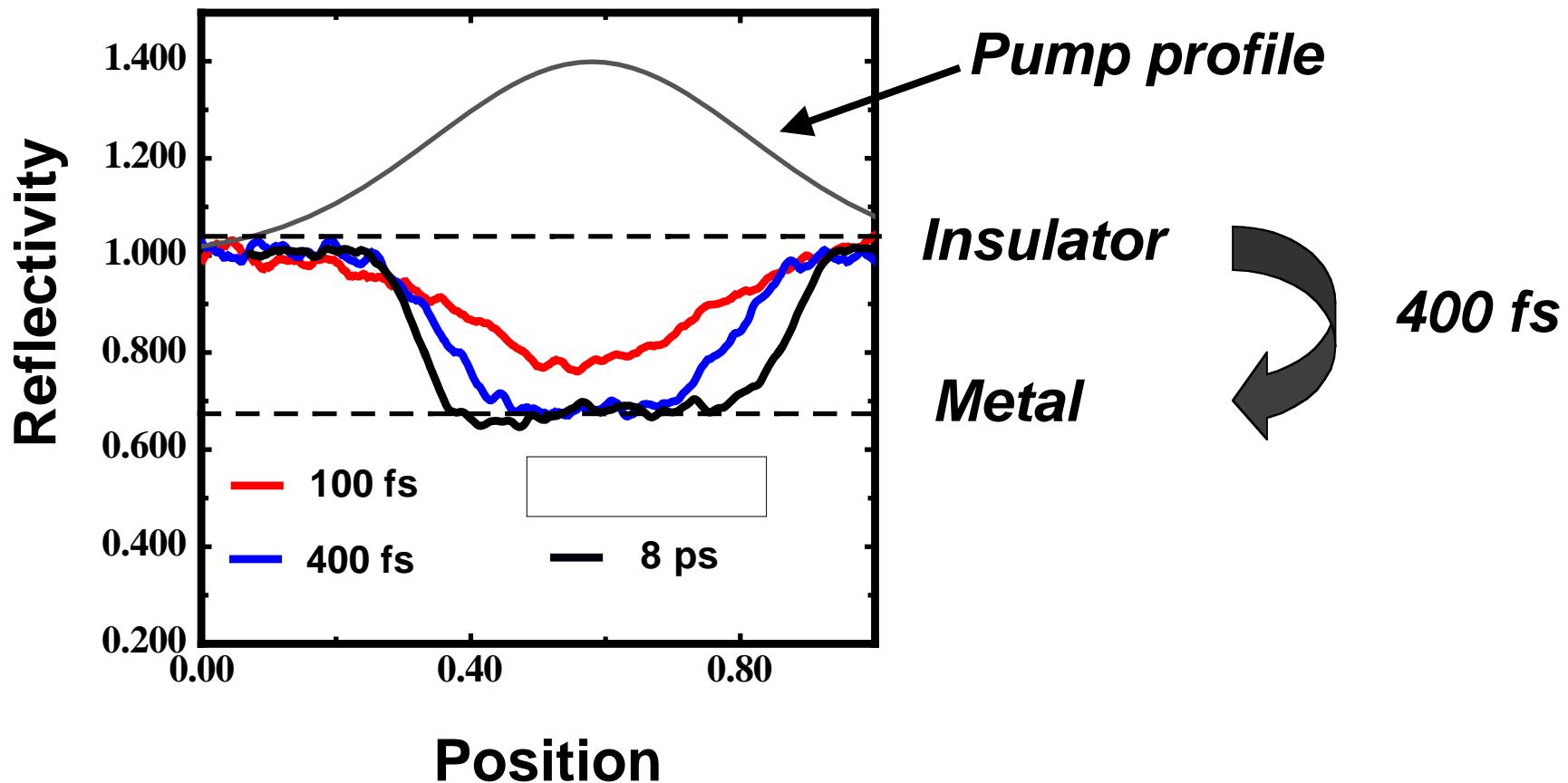
$T > 340 \text{ K}$

Rutile

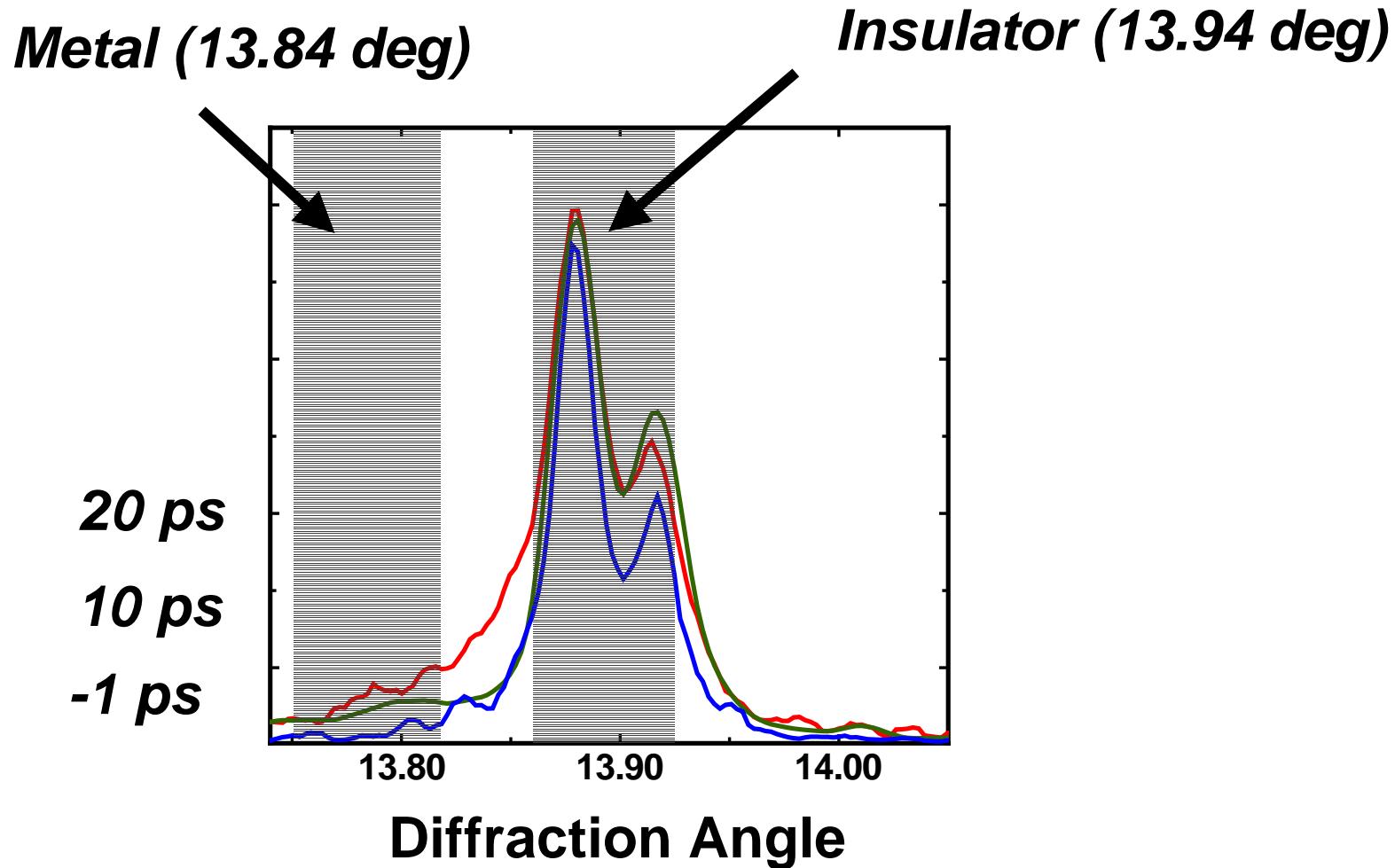
Metallic



Ultrafast Optical Data: Insulator to Metal



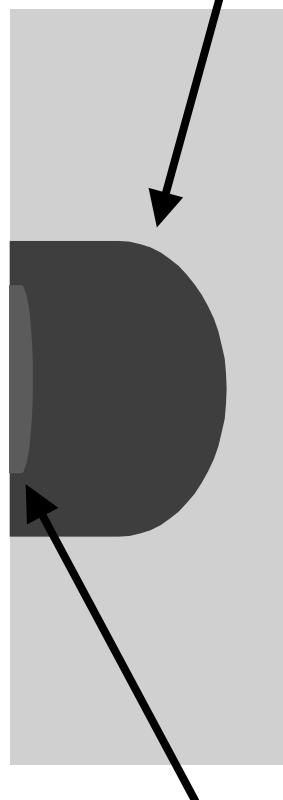
Ultrafast X-ray diffraction: bulk VO₂ (110)



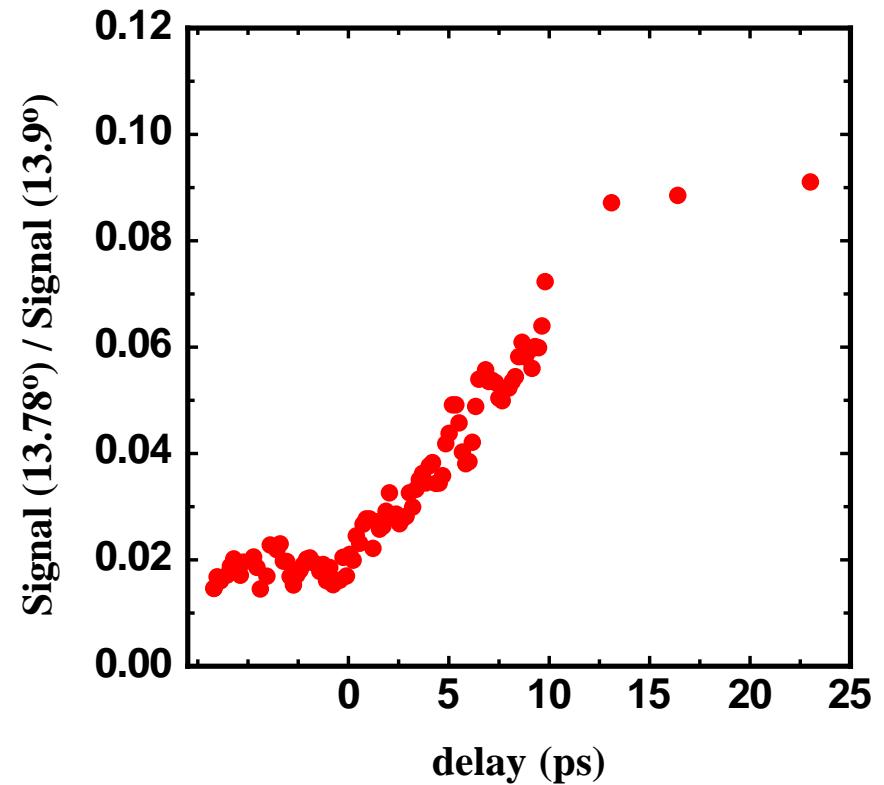
Time response



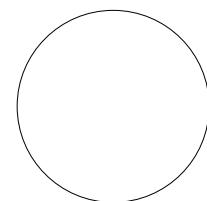
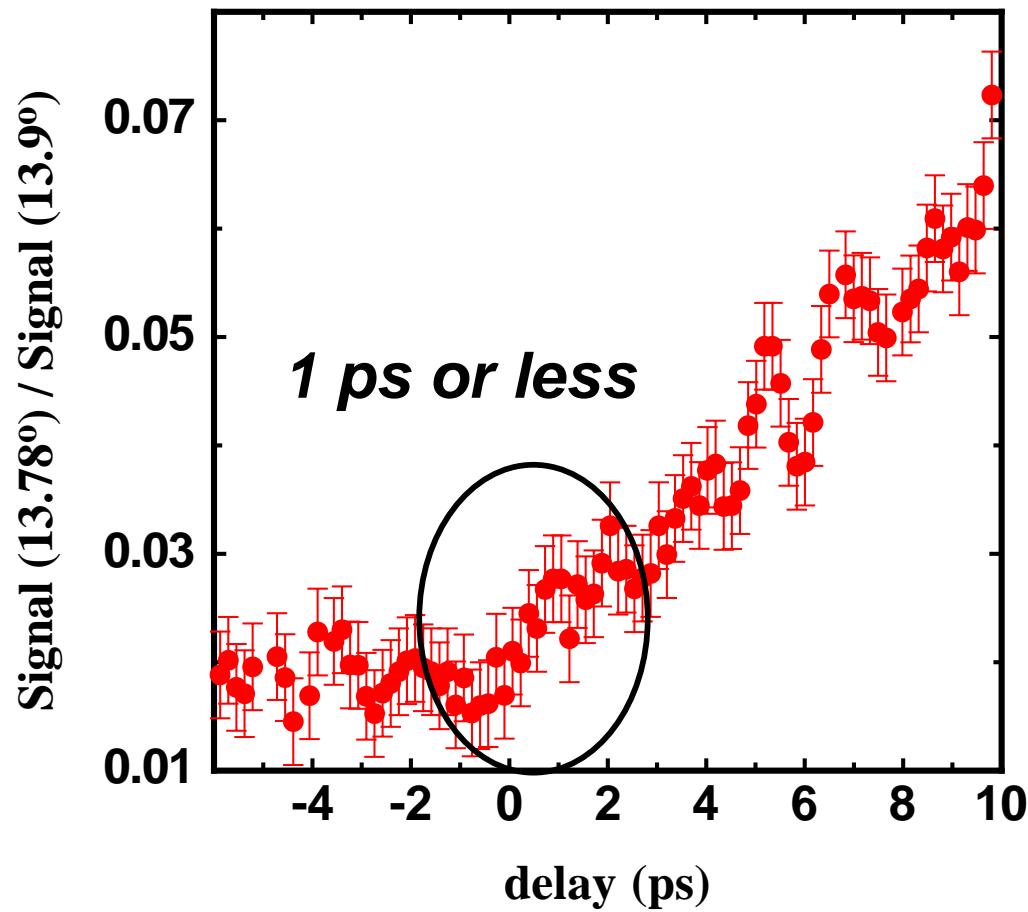
X-rays \approx 3000 nm



Metallic phase \approx 300 nm



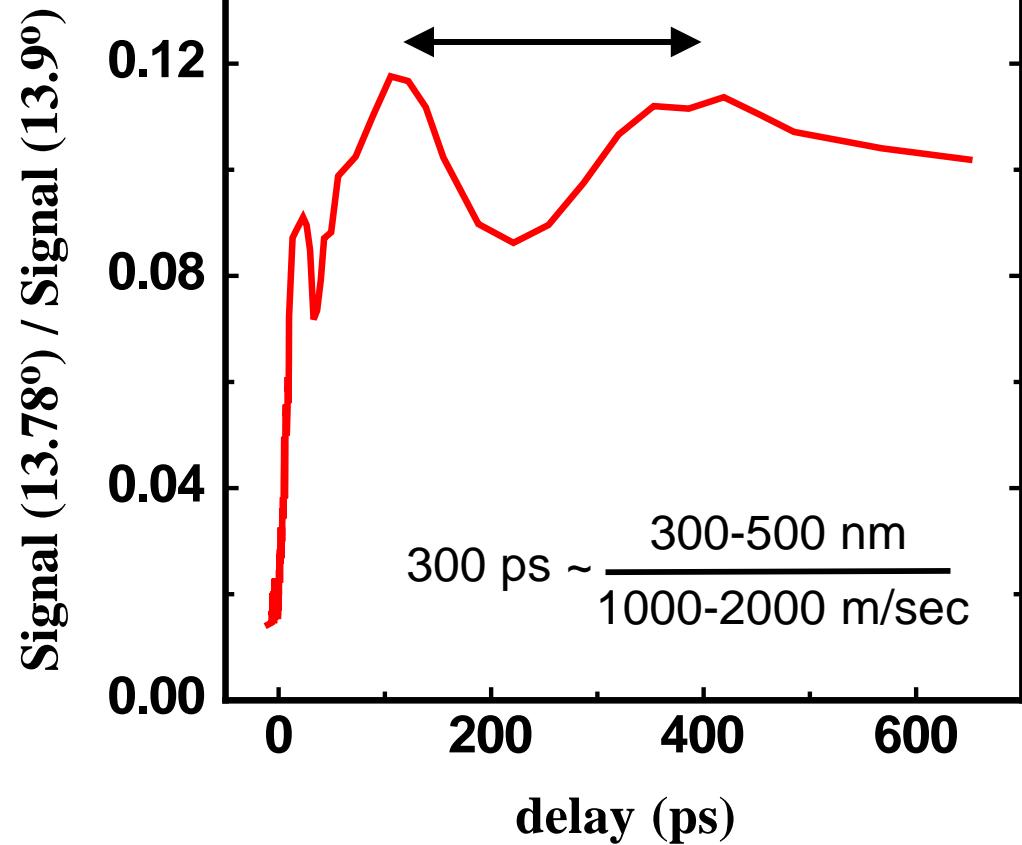
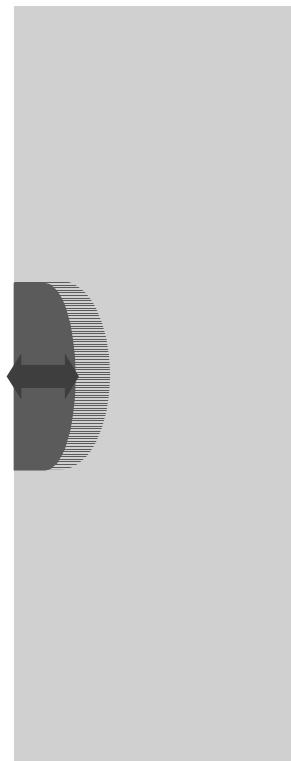
Time response



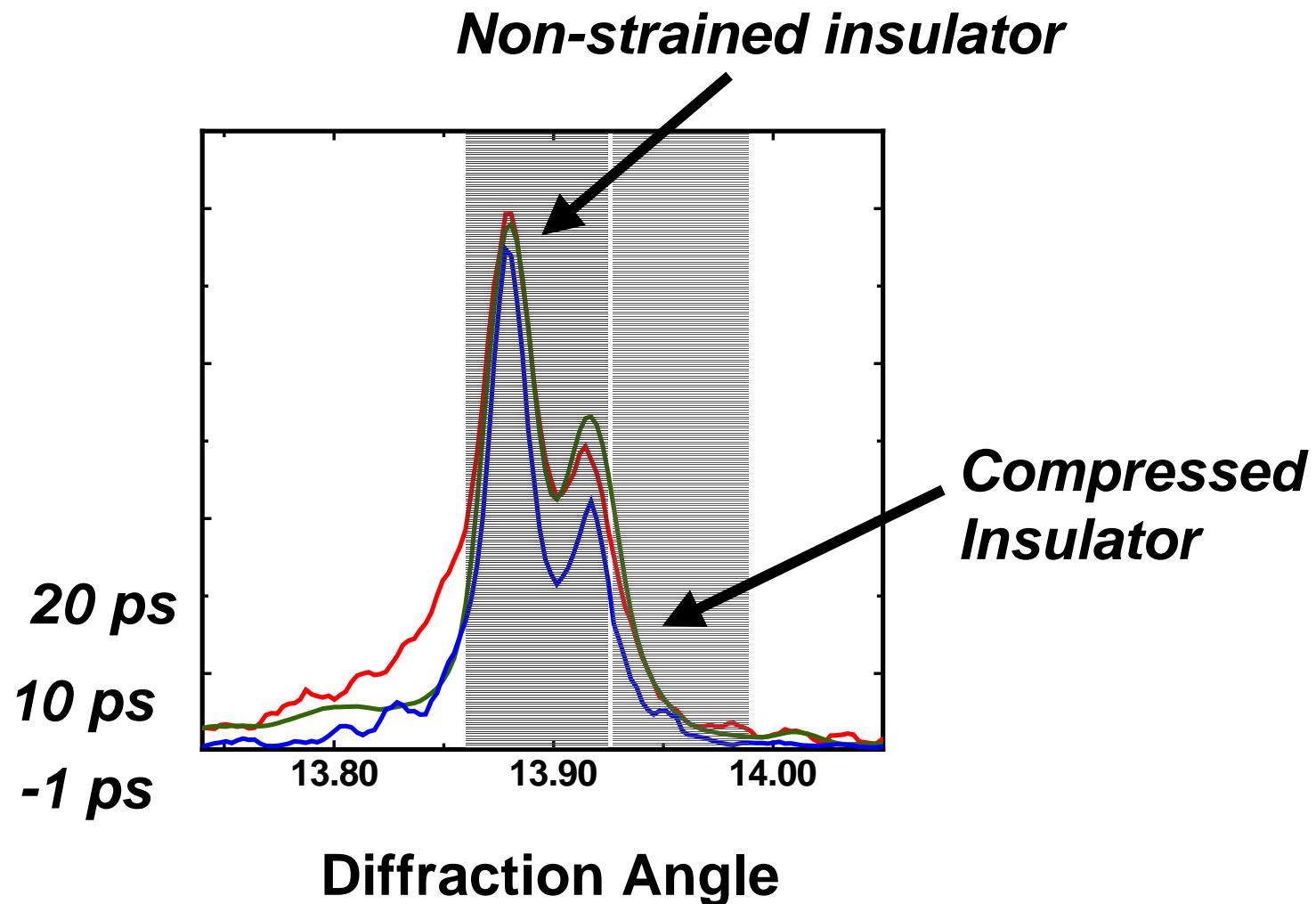
Long time response



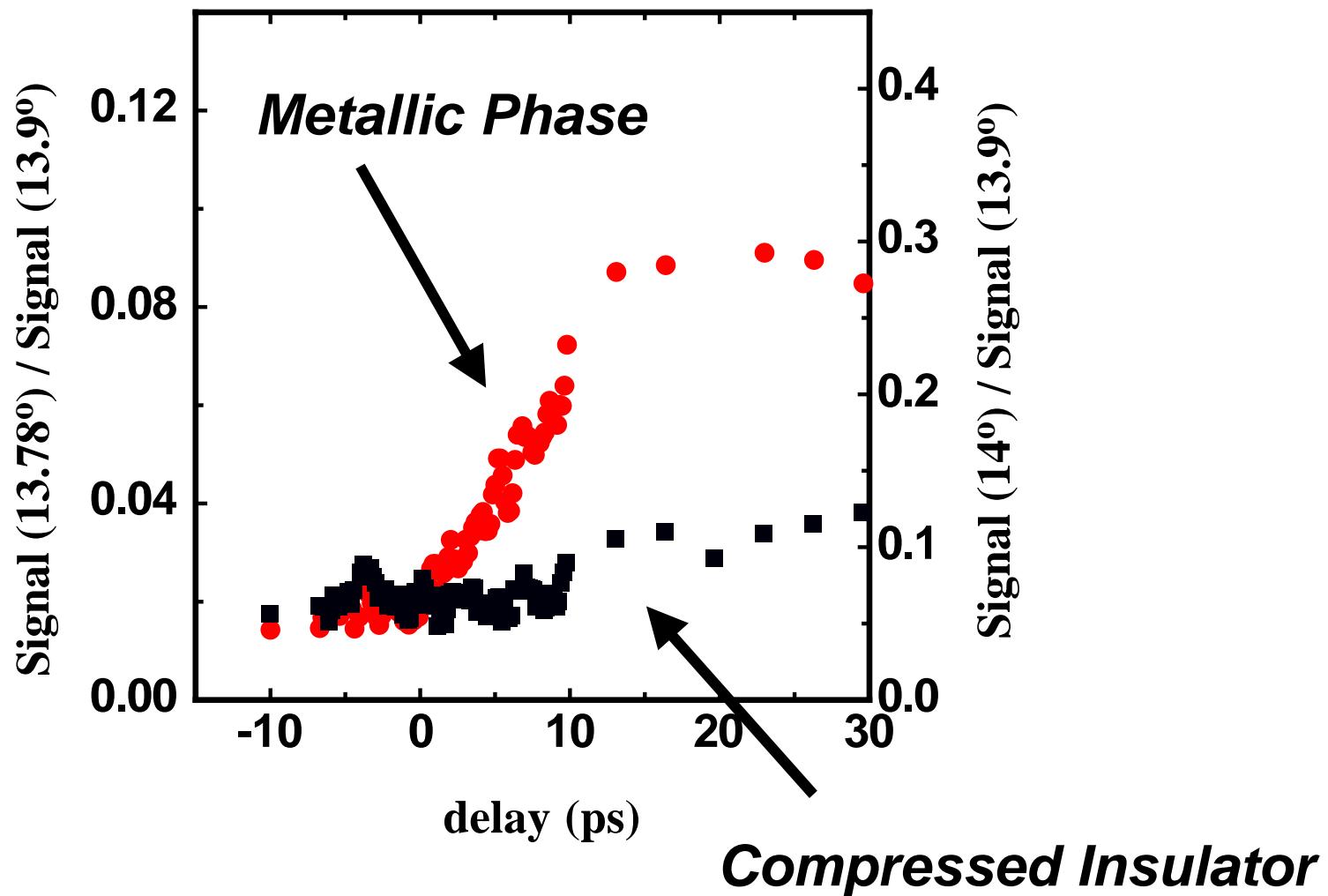
Acoustic response ?



Compression of the Insulating phase



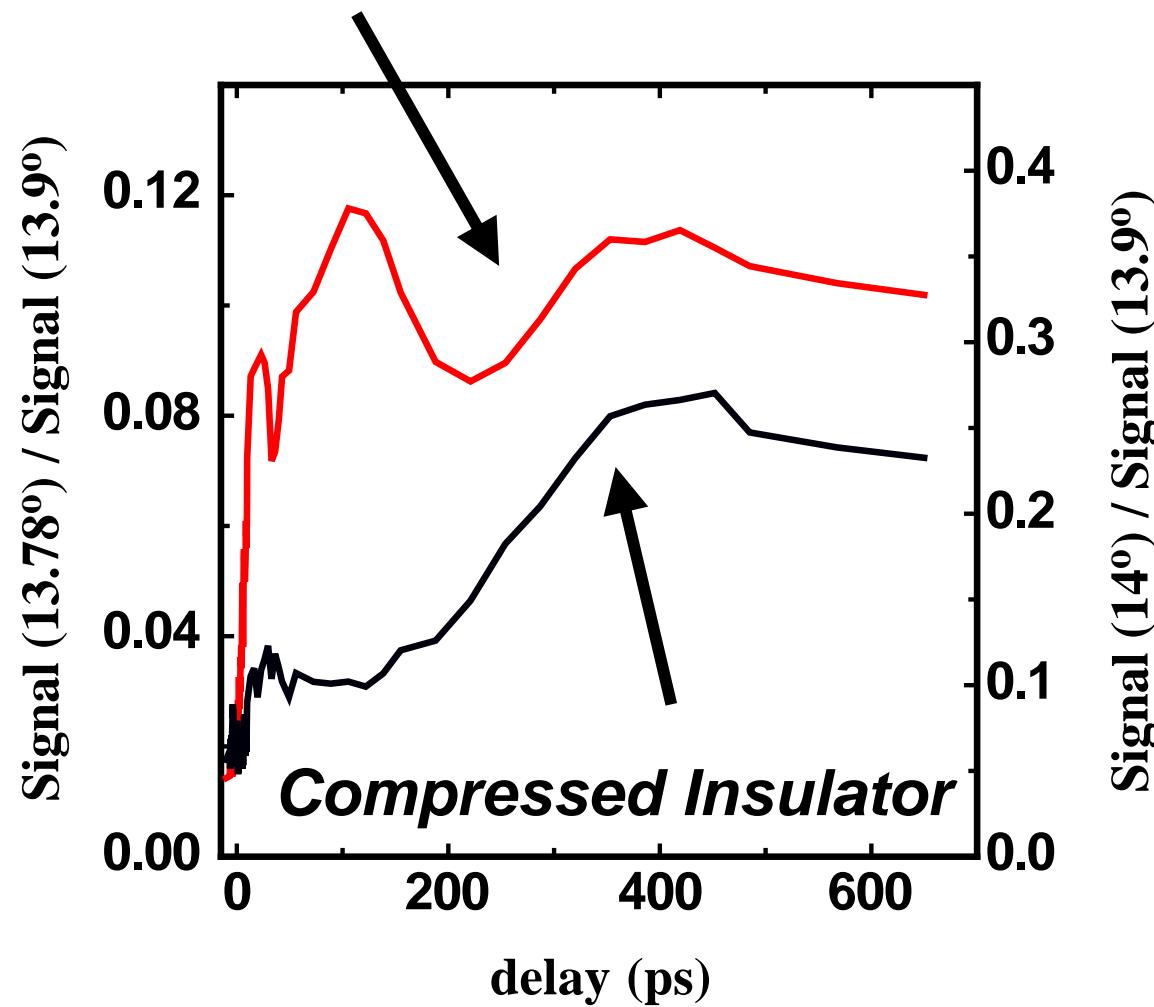
Compression of the insulating phase



Compression of the insulating phase

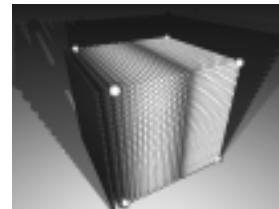


Metallic Phase



Summary and conclusion

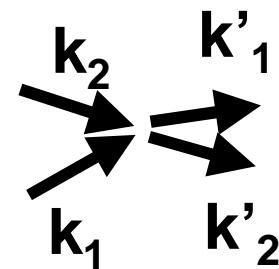
Coherent lattice transport



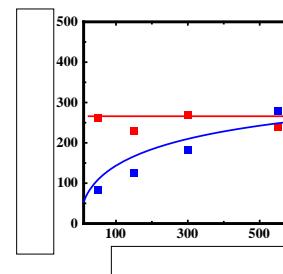
Lattice transport across buried interfaces



De-phasing of Acoustic phonons



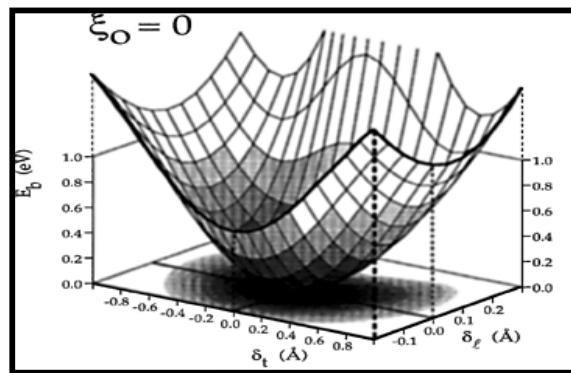
Heating depths and scaling laws for melting / ablation thresholds



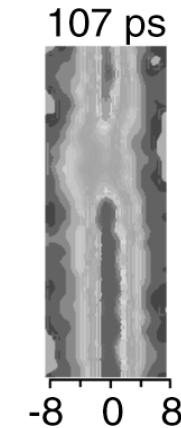
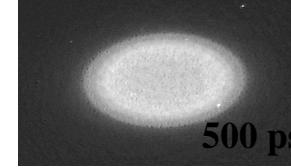
Conclusion



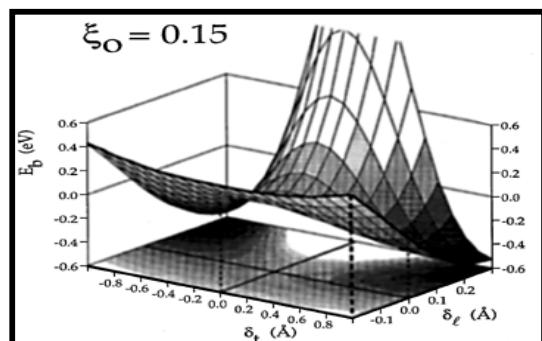
Thermal melting



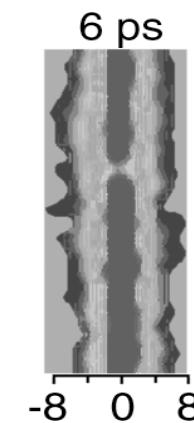
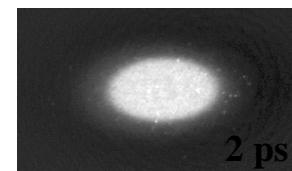
$t > 100 \text{ ps}$



Non-thermal melting



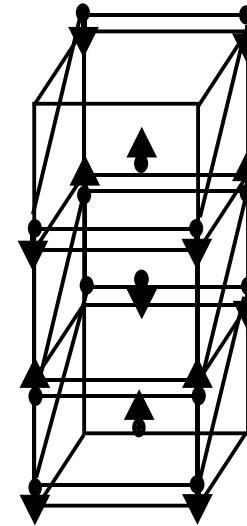
$t \approx 1 \text{ ps}$



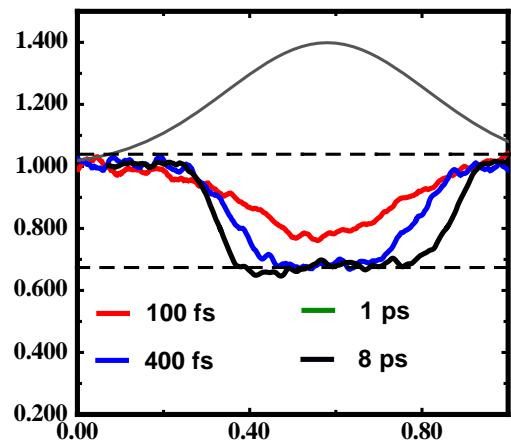
Conclusions



Solid-Solid phase transition in VO₂



Optical data



X-ray data

